Journal of Non-Crystalline Solids 97&98 (1987) 1473–1502
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AUTHOR INDEX

Abd-Elaal, M.M., see Kenawy 97/98 (1987) 1275
Abdulhalim, I., R. Beserman and Yu.L. Khait, Light induced structural changes in amorphous semiconductors 97/98 (1987) 387
Abe, K., see Nitta 97/98 (1987) 695
Abe, K., see Tsutsumi 97/98 (1987) 1063
Abeles, B., L. Yang, D. Leta and C. Majkrzak, Fast diffusion of interstitial deuterium in amorphous silicon 97/98 (1987) 353
Abeles, B., see Yang 97/98 (1987) 851
Abeles, B., see Grahn 97/98 (1987) 855
Abeles, B., see Sette 97/98 (1987) 895
Abeles, B., see Yang 97/98 (1987) 1155
Abkowitz, M., Space charge spectroscopic studies of localized states in glassy semiconductors *(Invited paper)* 97/98 (1987) 1163
Abkowitz, M.A., see Stolka 97/98 (1987) 1111
Adler, D., see Branz 97/98 (1987) 655
Adler, D., see Flint 97/98 (1987) 1419
Adriaenssens, G.J. and G. Seynhaeve, Relation between system parameters and measured drift mobilities in amorphous semiconductors 97/98 (1987) 133
Adriaenssens, G.J., see Seynhaeve 97/98 (1987) 607
Adriaenssens, G.J., P. Nagels and G. Seynhaeve, Steady-state photoconductivity in Bi- and Sb-modified Ge_2Se_7 glasses 97/98 (1987) 675
Agafonov, A.I., E.P. Domashevskaya, E.N. Desyatirikova, V.N. Seleznev, V.A. Terekhov and G.G. Eldarov, Changing of density of states in amorphous silicon nitride at degradation of its electric properties using soft X-ray spectroscopy 97/98 (1987) 827
Agarwal, S.C., see Guha 97/98 (1987) 1455
Agrawal, B.K. and S. Agrawal, Electronic structure of hydrogenated/fluorinated a-$Si_{1-x}Ge_x$ alloys 97/98 (1987) 507
Agrawal, B.K., P.S. Yadav and B.K. Ghosh, Vibrational excitations in a-Si_3N_4:H(D) alloys 97/98 (1987) 511
Agrawal, S., see Agrawal 97/98 (1987) 507
Akasaka, T., see Ohsawa 97/98 (1987) 91
Akita, S., see Nakayama 97/98 (1987) 743
Akita, S., see Nakayama 97/98 (1987) 1447
Aleksandrova, M.M., see Demishev 97/98 (1987) 1459
Aljishi, S., see Smith 97/98 (1987) 775
Aljishi, S., see Conde 97/98 (1987) 939
Aljishi, S., V. Chu, Z E. Smith, D.S. Shen, J.P. Conde, D. Slobodin, J. Kolodzey and S. Wagner, Steady state and transient transport in a-Si,Ge:H,F alloys 97/98 (1987) 1023
Allain, B., see Perrin 97/98 (1987) 261
Alonso, J.C., see Pickin 97/98 (1987) 599
Alvarez, F., see Pereyra 97/98 (1987) 871
Alvarez, F., H.L. Fragnito, P. Prieto and I. Chambouleyron, Visible light emission from reverse biased amorphous silicon carbide p-i-n structures 97/98 (1987) 1319
Amov, B., see Tsvetkova 97/98 (1987) 443

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Ananichev, V.A., see Koudelka 97/98 (1987) 1271
Anbutu, H., see Hasegawa 97/98 (1987) 1043
Andersen, O.K., see Bose 97/98 (1987) 459
Anderson, M.J., see Shimakawa 97/98 (1987) 623
Andrade, A.M., see Pereyra 97/98 (1987) 871
Andreev, A.A., see Kosarev 97/98 (1987) 615
Andriesh, A.M. and D.I. Tsiulyanu, Formation of gap edges and shift of Fermi level in As_2S_3-based glass alloys with addition of germanium 97/98 (1987) 1135
Angell, M., see Conde 97/98 (1987) 939
Antoine, A.M. and B. Drevillon, In-situ investigation of the early stage of the growth of a-Si:H on silica and tin dioxide substrates 97/98 (1987) 1403
Antonetti, A., see Fauchet 97/98 (1987) 145
Arai, T., see Onari 97/98 (1987) 1115
Arai, T., see Matsuishi 97/98 (1987) 1187
Arkhipov, V.I., A.I. Rudenko and S.D. Shutov, Transient hopping conductivity in amorphous semiconductors with non-equilibrium occupation of localized states 97/98 (1987) 129
Arlauskas, K., see Juška 97/98 (1987) 559
Asano, A., T. Ichimura, M. Ohsawa, H. Sakai and Y. Uchida, Characterization of a-$Si_{1-x}C_x$:H/a-Si:H and a-SiN_x:H/a-Si:H heterojunctions by photothermal deflection spectroscopy 97/98 (1987) 971
Ashworth, J., see Brunst 97/98 (1987) 1343
Audouard, A., see Por 97/98 (1987) 419
Austin, I.G., see Searle 97/98 (1987) 991
Averyanov, V.L., see Sarsembinov 97/98 (1987) 987

Babayev, A.A., see Konkov 97/98 (1987) 1391
Bacalis, N., see Economou 97/98 (1987) 101
Baert, K., see Symons 97/98 (1987) 1315
Baia, I., see Martins 97/98 (1987) 1399
Balabanov, S., see Tsvetkova 97/98 (1987) 443
Balagurov, L.A., E.M. Omeljanovsky, A.G. Petukhov, M.N. Starikov and M.G. Foigel, Optical transitions involving deep levels in amorphous semiconductors 97/98 (1987) 527
Bando, T., see Katyal 97/98 (1987) 1195
Bar-Yam, Y. and J.D. Joannopoulos, Theories of defects in amorphous semiconductors *(Invited paper)* 97/98 (1987) 467
Baranovskii, S.D., V.G. Karpov and B.I. Shklovskii, Theory of nonradiative recombination in amorphous semiconductors 97/98 (1987) 487
Barclay, R.P., J.L. Brebner, G. Perluzzo and G. Seynhaeve, Effects of deep trapping and band bending on the transient photodecay in a-Si:H 97/98 (1987) 603
Barclay, R.P., see Seynhaeve 97/98 (1987) 607
Barclay, R.P., M. Sarr and J.L. Brebner, Reversible metastable defect centres in amorphous arsenic triselenide 97/98 (1987) 687
Bárdoš, L., V. Dušek and M. Vaněček, New way for high-rate a-Si deposition 97/98 (1987) 281
Baron, R., see Talamantes 97/98 (1987) 555
Barrio, R., J. Tagueña-Martinez and E. Sansores, Carbon in silicon: a cluster calculation 97/98 (1987) 499
Basa, D.K., see Mui 97/98 (1987) 999
Bauer, G.H., see Weller 97/98 (1987) 1071
Bauer, G.H., see Mohring 97/98 (1987) 1415
Bayliss, S.C., see Piggins 97/98 (1987) 1047
Beck, G., see Finger 97/98 (1987) 1015

Bedel'bayeva, G.E., A.V. Kolobov, B.T. Kolomiets, V.M. Lyubin and M.A. Taguirdzhanov, Photodoping of As–S films with group II metals 97/98 (1987) 1243
Belford, R., see Hajto 97/98 (1987) 1191
Belin, E., see Theye 97/98 (1987) 1107
Bell, F.G. and L. Ley, Photoemission in SiO_x alloys 97/98 (1987) 1007
Bellissent, R., Structure of amorphous semiconductors by small angle scattering *(Invited paper)* 97/98 (1987) 329
Bellissent, R., C. Bergman, A. Pellegatti, R. Ceolin and J.P. Gaspard, Liquid arsenic: a Peierls distortion in the liquid – experimental results and computer simulation 97/98 (1987) 1263
Bellissent, R., see Gaspard 97/98 (1987) 1283
Benferhat, R. and B. Drevillon, Infrared ellipsometry study of the vibrational properties of a-Si:H, a-SiC:H and a-SiGe:H ultrathin films 97/98 (1987) 835
Bergman, C., see Bellissent 97/98 (1987) 1263
Bergman, C., see Gaspard 97/98 (1987) 1283
Bergner, H., V. Brückner, M. Lenzner and W. Nowick, Application of amorphous silicon for picosecond optoelectronic switching 97/98 (1987) 1335
Berkin, J., see Main 97/98 (1987) 779
Berner, H., P. Munz, E. Bucher, F. Kessler and S.M. Paasche, Photoemission and density of states in amorphous silicon 97/98 (1987) 847
Bernholc, J., see Wong 97/98 (1987) 1171
Beserman, R., see Abdulhalim 97/98 (1987) 387
Beyer, W., see Foller 97/98 (1987) 567
Beyer, W., see Petrova-Koch 97/98 (1987) 807
Beyer, W., C.E. Gatts, J. Herion, W. Losch and H. Wagner, Formation of platinum silicide on hydrogenated amorphous silicon 97/98 (1987) 951
Beyer, W., Structural and electronic properties of silicon-based amorphous alloys *(Invited paper)* 97/98 (1987) 1027
Bezemer, J., see Landweer 97/98 (1987) 711
Bhat, P.K., see Hollingsworth 97/98 (1987) 309
Bhat, P.K., H. Chatham, Y.H. Shing and J.W. Perry, The growth of glow discharge hydrogenated amorphous silicon 97/98 (1987) 1383
Bichara, C., see Gaspard 97/98 (1987) 1283
Bischoff, J.L., L. Kubler and D. Bolmont, Low temperature nitridation and hydrogenation of Si films with NH_3: a photoemission study 97/98 (1987) 1407
Bishop, S.G., see Strom 97/98 (1987) 1183
Biskupski, G. and A. Briggs, Hopping conduction and creation of a Coulomb gap by a magnetic field in InP 97/98 (1987) 683
Böhm, M., S. Salamon and Z. Kiss, Evaluation of the density of states at a-Si/SiN_x/Cr capacitors by means of the quasi-static slow ramp *CV*-method 97/98 (1987) 735
Bolmont, D., see Bischoff 97/98 (1987) 1407
Bolmont, D., see Muller 97/98 (1987) 1411
Boonstra, A.J., see Schropp 97/98 (1987) 1339
Borisova, Z.U., see Chepeleva 97/98 (1987) 659
Bork, V.P., see Fedders 97/98 (1987) 357
Boscherini, F., see Evangelisti 97/98 (1987) 407
Bose, S.K., K. Winer and O.K. Andersen, Electronic properties of a realistic model of amorphous silicon 97/98 (1987) 459
Böttger, H. and D. Wegener, Theory of high-field hopping transport *(Invited paper)* 97/98 (1987) 547
Boyce, J.B., S.E. Ready and C.C. Tsai, Local structure of dopants in compensated and singly-doped amorphous silicon 97/98 (1987) 345

Boyce, J.B., see Fedders 97/98 (1987) 357
Branz, H.M., D. Adler and M. Silver, Theory of sweep-out experiments: a new spectroscopy for the electronic density of states in doped hydrogenated amorphous silicon films 97/98 (1987) 655
Branz, H.M., see Flint 97/98 (1987) 1419
Brebner, J.L., see Barclay 97/98 (1987) 603
Brebner, J.L., see Barclay 97/98 (1987) 687
Briggs, A., see Biskupski 97/98 (1987) 683
Brückner, V., see Bergner 97/98 (1987) 1335
Brunst, G., H. Harms, J. Ashworth, K.H. Rosan and K. Kempter, a-Si:H TFTs and their application in linear image sensors 97/98 (1987) 1343
Brutscher, N., see Hoheisel 97/98 (1987) 959
Bruyère, J.-C., see Vaillant 97/98 (1987) 639
Bucher, E., see Berner 97/98 (1987) 847
Bugmann, G., Optical emission profiles used for a-Si:H deposition rate calculation 97/98 (1987) 1423
Bulka, B.R., Conductance of a series of metallic rings in a magnetic field 97/98 (1987) 249
Bullemer, B., see Kusian 97/98 (1987) 647
Burattini, E., see Dalba 97/98 (1987) 411
Burnett, J.H., see MacKenzie 97/98 (1987) 1019
Bychkov, E.A., see Chepeleva 97/98 (1987) 659

Cai, P.-X., see Wang 97/98 (1987) 1039
Cannella, V., see Silver 97/98 (1987) 305
Čápek, V., Generalized master equations and the phonon-assisted hopping 97/98 (1987) 475
Capizzi, M., see Mariucci 97/98 (1987) 1075
Caplin, A.D., see Hedges 97/98 (1987) 1279
Capozi, M., see Quaresima 97/98 (1987) 979
Card, H.C., see Herak 97/98 (1987) 277
Carius, R., see Jahn 97/98 (1987) 575
Carius, R., see Finger 97/98 (1987) 1015
Carius, R., F. Finger and W. Fuhs, Photoluminescence of doped and undoped amorphous Si/Ge alloys 97/98 (1987) 1067
Carreno, M.N.P., see Pereyra 97/98 (1987) 871
Carvalho, N., see Martins 97/98 (1987) 1399
Cavese, J.M., see Collins 97/98 (1987) 269
Cavese, J.M., see Collins 97/98 (1987) 1439
Ceolin, R., see Bellissent 97/98 (1987) 1263
Červinka, L., O. Smotlacha and L. Tichý, A study of the structure of $(GeS_2)_{1-x}(Sb_2S_3)_x$ glasses 97/98 (1987) 183
Červinka, L., Comments on medium-range ordering in non-crystalline solids *(Organizer's summary)* 97/98 (1987) 207
Chahed, L., G. Vuye, M.L. Thèye, Y.M. Li, K.D. MacKenzie and W. Paul, Comparative study of the optical absorption spectra of amorphous hydrogenated silicon derived from photothermal deflection spectrosocopy and photoconductivity measurements 97/98 (1987) 727
Chambouleyron, I., see Alvarez 97/98 (1987) 1319
Chatham, H., see Bhat 97/98 (1987) 1383
Chau, T.T., see Herak 97/98 (1987) 277
Chechetkina, E.A., see Dembovsky 97/98 (1987) 427
Chen, G.H., see Zhang 97/98 (1987) 1311
Chen, H., see Chen 97/98 (1987) 341
Chen, K., G. Mao, D. Feng, Y. Yan, J. Du, Z. Li, H. Chen and H. Fritzsche, Quasiperiodic a-Si:H/a-SiN_x:H multilayer structures 97/98 (1987) 341

Chen, W., see Xu 97/98 (1987) 983
Cheng, R.G., see Zhang 97/98 (1987) 923
Cheng, R.-G., see Wang 97/98 (1987) 1039
Chepeleva, I.V., Z.U. Borisova, Yu.G. Vlasov and E.A. Bychkov, ESR and Mössbauer spectroscopy of iron-doped Ag–As–S and Ge–Sb–Se glasses 97/98 (1987) 659
Chepeleva, I.V., Paramagnetic radiation defects in chalcogenide glasses and glassy Se 97/98 (1987) 1179
Chicon, R., see Hadley 97/98 (1987) 233
Chicon, R., M. Ortuño, B. Hadley, M. Green and M. Pollak, Hard gaps in localized interacting systems 97/98 (1987) 237
Chieux, P., see Gaspard 97/98 (1987) 1283
Choi, S.-H., B.-S. Yoo, C. Lee and J. Jang, Photo and bias effects in coplanar conductance of doping-modulated amorphous silicon superlattices 97/98 (1987) 911
Choi, W.K., S. Reynolds, J. Hajto, S.M. Gage, A.E. Owen, A.J. Snell, I.M. Flanagan, M.J. Rose, F.J. Djamdji, P.G. LeComber and W.E. Spear, Pre-formed J–V and C–V characteristics of a-Si:H p^+ ni junctions 97/98 (1987) 1331
Christou, A., see Zdetsis 97/98 (1987) 831
Chu, V., see Aljishi 97/98 (1987) 1023
Chuang, T.C., L.E. Fennell, W.B. Jackson, J. Levine, M.J. Thompson, H.C. Tuan, R. Weisfield, T. Hamano, H. Itoh, T. Ozawa and S. Tomiyama, Large-area a-Si:H TFT arrays for printing, input scanning and electronic copying applications 97/98 (1987) 301
Cimino, R., see Evangelisti 97/98 (1987) 407
Cimpl, Z., F. Kosek and F. Lukeš, The structure of As_2S_3 thin films 97/98 (1987) 439
Cloude, C., see Spear 97/98 (1987) 15
Cohen, J.D., see Gelatos 97/98 (1987) 71
Cohen, J.D., see Michelson 97/98 (1987) 763
Cohen, J.D., J.M. Essick, C.E. Michelson and J.P. Harbison, Defect formation in amorphous silicon doping superlattice films 97/98 (1987) 875
Cohen, M.H., see Economou 97/98 (1987) 101
Collins, R.W., see Gustafson 97/98 (1987) 121
Collins, R.W. and J.M. Cavese, Initial nucleation of a-Si:H: an in situ ellipsometry study of the effect of deposition procedure 97/98 (1987) 269
Collins, R.W. and J.M. Cavese, Surface structure of glow discharge a-Si:H: Implications for multilayer film growth 97/98 (1987) 1439
Coluzza, C., see Quaresima 97/98 (1987) 979
Conde, J.P., see Fauchet 97/98 (1987) 145
Conde, J.P., S. Aljishi, D.S. Shen, M. Angell and S. Wagner, Carrier transport mechanisms in a-Si:H,F/a-Si,Ge:H,F superlattices 97/98 (1987) 939
Conde, J.P., see Aljishi 97/98 (1987) 1023
Corderman, R., see Mui 97/98 (1987) 999
Coscia, U., see Mariucci 97/98 (1987) 1075
Cros, Y., see Rostaing 97/98 (1987) 1051
Cuniot, M., J. Dixmier and R. Mosseri, Topological order in a-$Si_{1-x}Ge_x$:H alloys: experimental X-ray diffraction study and theoretical simulation in relation with composition 97/98 (1987) 171
Curtins, H., see Favre 97/98 (1987) 731
Curtins, H., see Schwarz 97/98 (1987) 759

Dalba, G., P. Fornasini, G. Giunta, E. Burattini and A. Tomasi, Local structure in non-crystalline Sb–S semiconductors 97/98 (1987) 411
Davis, E.A., see Piggins 97/98 (1987) 1047
Davis, E.A., see Derbyshire 97/98 (1987) 1103

Deguchi, M., see Kruangam 97/98 (1987) 293
Deiss, J.L., B.E. Drissi, M. Robino, M. Tapiero, J.P. Zielinger and R. Weil, Properties of amorphous Zn_3P_2 97/98 (1987) 679
Della Sala, D., see Fortunato 97/98 (1987) 423
Della Sala, D., see Mariucci 97/98 (1987) 1075
Dembovsky, S.A., L.M. Ilizarov and E.A. Chechetkina, Amorphous semiconductors prepared by rapid solidification 97/98 (1987) 427
Demishev, S.V., Yu.V. Kosichkin, A.G. Lyapin, N.E. Sluchanko, M.M. Aleksandrova, V.I. Larchev, S.V. Popova and G.G. Skrotskaya, The bulk amorphous A^3B^5 semiconductor: Technological and physical aspects 97/98 (1987) 1459
Deneuville, A., see Valentin 97/98 (1987) 583
Derbyshire, H.S., S.J. Gurman and E.A. Davis, Preparation and properties of amorphous Cd–Si–As thin films 97/98 (1987) 1103
Desyatirikova, E.N., see Agafonov 97/98 (1987) 827
Dixmier, J., see Cuniot 97/98 (1987) 171
Dixmier, J., see Essamet 97/98 (1987) 191
Djakov, A., see Tsvetkova 97/98 (1987) 443
Djamdji, F., P.G. LeComber, R. Schumacher, P. Thomas and K. Weber, Determination of the microscopic prefactor of the conductivity of a-Si:H using temperature dependent field-effect measurements 97/98 (1987) 543
Djamdji, F.J., see Choi 97/98 (1987) 1331
Domashevskaya, E.P., see Agafonov 97/98 (1987) 827
Dong, B., see Gu 97/98 (1987) 479
Dragomir, A., see Popescu 97/98 (1987) 1431
Draijer, A., M.A. Haghani, M. von Hartrott, K. Ott, C.A. Paulick, D. Quitmann and B. Sauer, Impurities in liquid semiconductors, studied by TDPAD technique 97/98 (1987) 1287
Drchal, V. and J. Málek, Atomic and electronic structure of amorphous carbon based on the large-scale CRN model 97/98 (1987) 199
Drevillon, B., see Godet 97/98 (1987) 431
Drevillon, B., see Benferhat 97/98 (1987) 835
Drevillon, B., see Antoine 97/98 (1987) 1403
Driss-Khodja, M., see Solomon 97/98 (1987) 1091
Drissi, B.E., see Deiss 97/98 (1987) 679
Du, J., see Chen 97/98 (1987) 341
Ducharme, S., see Durny 97/98 (1987) 927
Dunnett, B., see LeComber 97/98 (1987) 1003
Dupin, J., see Theye 97/98 (1987) 1107
Durny, R., S. Ducharme, J. Viner, P.C. Taylor and D. Haneman, Absorption in amorphous silicon doping-modulated multilayers 97/98 (1987) 927
Dušek, V., see Bárdoš 97/98 (1987) 281
Dzakelov, S.A., see Sarsembinov 97/98 (1987) 987

Eberhardt, W., see Yang 97/98 (1987) 851
Economou, E.N., N. Bacalis and M.H. Cohen, Exponential tails in the density of states 97/98 (1987) 101
Efros, A.L. and B.I. Shklovskii, Influence of electron–electron interaction on hopping conduction of disordered systems 97/98 (1987) 31
Eggert, J.R., see MacKenzie 97/98 (1987) 1019
El-Fouly, M.H., see Kotkata 97/98 (1987) 1259
Eldarov, G.G., see Agafonov 97/98 (1987) 827
Elliott, S.R., Medium-range order in amorphous materials: documented cases 97/98 (1987) 159
Elliott, S.R., see Gladden 97/98 (1987) 383
Elliott, S.R., see Gladden 97/98 (1987) 1175

Elliott, S.R., see Spence 97/98 (1987) 1215
Elliott, S.R., see Rennie 97/98 (1987) 1239
Essamet, M., B. Hepp, N. Proust and J. Dixmier, Investigation of the structural disorder fluctuations in a-Si:H films by coupled X ray diffractometry and photodeflection spectroscopy 97/98 (1987) 191
Esser, B., On the theory of band tail relaxation in disordered systems 97/98 (1987) 137
Essick, J.M., see Cohen 97/98 (1987) 875
Evangelisti, F., see Filipponi 97/98 (1987) 403
Evangelisti, F., F. Boscherini, R. Cimino, F. Patella, P. Perfetti and C. Quaresima, Local order in silicon–germanium alloys and at silicon–germanium heterojunctions by analysis of Ge 3d core levels 97/98 (1987) 407
Evangelisti, F., see Mariucci 97/98 (1987) 1075
Ewen, P.J.S., A. Zakery, A.P. Firth and A.E. Owen, Compositional dependence of photodissolution kinetics in amorphous As–S films 97/98 (1987) 1127
Ewen, P.J.S., see Hajto 97/98 (1987) 1191

Fauchet, P.M., D. Hulin, A. Migus, A. Antonetti, J.P. Conde and S. Wagner, Femtosecond spectroscopy in amorphous silicon and silicon–germanium alloys 97/98 (1987) 145
Fauchet, P.M. and K.D. Li, The dielectric function of laser-produced molten Si 97/98 (1987) 1267
Favre, M., H. Curtins and A.V. Shah, Study of surface/interface and bulk defect density in a-Si:H by means of photothermal deflection spectroscopy and photoconductivity 97/98 (1987) 731
Fayek, S.A., see Kotkata 97/98 (1987) 1259
Fedders, P.A., V.P. Bork, D.J. Leopold, R.E. Norberg, J.B. Boyce and J.C. Knights, Annealing of weakly bound deuterium in a-Si:D,H 97/98 (1987) 357
Fei, Q., see Su 97/98 (1987) 1363
Fekeshgazi, I.V., see Lisitsa 97/98 (1987) 1159
Feltz, A., see Schirrmeister 97/98 (1987) 523
Feng, D., see Chen 97/98 (1987) 341
Feng, X., H. Liu, W. Tang and Z. Li, New results on photoluminescence spectra of a-Si:H/a-SiN_x:H multilayer structures 97/98 (1987) 915
Fennell, L.E., see Chuang 97/98 (1987) 301
Ferrazza, F., see Mariucci 97/98 (1987) 1075
Filipponi, A., see Mobilio 97/98 (1987) 365
Filipponi, A., F. Evangelisti and S. Mobilio, Vibrational correlation function in amorphous covalent solids 97/98 (1987) 403
Finger, F., see Schneider 97/98 (1987) 795
Finger, F., W. Fuhs, G. Beck and R. Carius, Defect states in a-$Si_{1-x}Ge_x$:H studied by electron spin resonance 97/98 (1987) 1015
Finger, F., see Carius 97/98 (1987) 1067
Finger, F., see Liedtke 97/98 (1987) 1083
Firth, A.P., see Ewen 97/98 (1987) 1127
Fischer, R., E.O. Göbel and G. Noll, Picosecond non-geminate carrier recombination in a-Si:H 97/98 (1987) 591
Fischer, R., see Gross 97/98 (1987) 643
Fisson, S., see Flank 97/98 (1987) 435
Flanagan, I.M., see Choi 97/98 (1987) 1331
Flank, A.M., P. Lagarde, D. Udron, S. Fisson, A. Gheorghiu and M.L. Theye, EXAFS study of the local atomic structure in amorphous InP 97/98 (1987) 435
Flint, J.H., H.M. Branz, C.J. Harris, J.S. Haggerty and D. Adler, Boron incorporation in hydrogenated amorphous silicon films prepared by chemical vapor deposition 97/98 (1987) 1419

Foigel, M.G., see Balagurov 97/98 (1987) 527
Foller, M., J. Herion, W. Beyer and H. Wagner, Surface photovoltage in a-Si:H 97/98 (1987) 567
Fong, C.Y., see Nichols 97/98 (1987) 495
Fornasini, P., see Dalba 97/98 (1987) 411
Fortunato, E., see Martins 97/98 (1987) 1399
Fortunato, G. and D. Della Sala, Evidence of two-phase structure in amorphous silicon oxides produced by $N_2O + SiH_4$ glow-discharge decomposition 97/98 (1987) 423
Fortunato, G., Determination of localized state energy distribution in a-Si:H by modulated photocurrent 97/98 (1987) 739
Fournier, J.P., see Yang 97/98 (1987) 1303
Fragnito, H.L., see Alvarez 97/98 (1987) 1319
Freitas Jr, J.A., see Strom 97/98 (1987) 1183
French, I.D., see Powell 97/98 (1987) 321
Fritzsche, H., The nature and energies of gap states in a-Si:H *(Organizer's summary)* 97/98 (1987) 95
Fritzsche, H., see Chen 97/98 (1987) 341
Fritzsche, H., see Vomvas 97/98 (1987) 823
Fritzsche, H., see Takada 97/98 (1987) 907
Fritzsche, H., see Wang 97/98 (1987) 919
Fritzsche, H., see Zhang 97/98 (1987) 923
Frumar, M. and L. Tichý, n-Type conductivity in chalcogenide glasses and layers *(Invited paper)* 97/98 (1987) 1139
Frumar, M., see Vlček 97/98 (1987) 1223
Fu, Z., see Yang 97/98 (1987) 851
Fuhs, W., see Jahn 97/98 (1987) 575
Fuhs, W., see Finger 97/98 (1987) 1015
Fuhs, W., see Carius 97/98 (1987) 1067
Fuhs, W., see Liedtke 97/98 (1987) 1083
Füstöss-Wégner, M., D.-S. Kim, H.-S. Pak, Gy. Zentai and L. Pogány, Effect of microinhomogeneities on collection efficiency spectra in (p-i-n) a-Si:H junctions 97/98 (1987) 1327

Gage, S.M., see Choi 97/98 (1987) 1331
Gaspard, J.P., see Mosseri 97/98 (1987) 415
Gaspard, J.P., see Bellissent 97/98 (1987) 1263
Gaspard, J.P., C. Bergman, C. Bichara, R. Bellissent, P. Chieux and J. Goffart, Structure of liquid II–IV compounds: CdTe 97/98 (1987) 1283
Gatts, C.E., see Beyer 97/98 (1987) 951
Geerts, M.J., see Van Oort 97/98 (1987) 1427
Gelatos, A.V. and J.D. Cohen, Capacitance studies of optical and thermal transitions from mobility gap states in hydrogenated amorphous silicon 97/98 (1987) 71
Gerl, M., see Por 97/98 (1987) 419
Gheorghiu, A., see Flank 97/98 (1987) 435
Gheorghiu, A., see Theye 97/98 (1987) 1107
Ghosh, B.K., see Agrawal 97/98 (1987) 511
Gibson, R., see LeComber 97/98 (1987) 1003
Gibson, R.A., see Hopkinson 97/98 (1987) 883
Girginoudi, D., see Zdetsis 97/98 (1987) 831
Giunta, G., see Dalba 97/98 (1987) 411
Gladden, L.F. and S.R. Elliott, Computer-generated models of a-$SiSe_2$: evidence for a glass exhibiting medium-range order 97/98 (1987) 383

Gladden, L.F. and S.R. Elliott, NMR studies of defect states in glassy selenium 97/98 (1987) 1175
Glatfelter, T., see Yang 97/98 (1987) 1303
Göbel, E.O., see Noll 97/98 (1987) 141
Göbel, E.O., see Fischer 97/98 (1987) 591
Godet, C., B. Drevillon and C. Senemaud, Electronic structure studies of amorphous and microcrystalline germanium 97/98 (1987) 431
Goedecker, S., see Schwarz 97/98 (1987) 759
Goffart, J., see Gaspard 97/98 (1987) 1283
Goldie, D., see Spear 97/98 (1987) 15
Götze, W. and P. Thomas, Principal results of the mode coupling approach to the conductor–insulator transition in strongly disordered systems 97/98 (1987) 217
Grahn, H.T., Z. Vardeny, H.J. Maris, J. Tauc and B. Abeles, Picosecond photoinduced electronic and acoustic effects in a-Si:H based multilayer structures 97/98 (1987) 855
Gray, J.L., see Turner 97/98 (1987) 1307
Green, M., see Hadley 97/98 (1987) 233
Green, M., see Chicon 97/98 (1987) 237
Griep, S., E. Lüder and T. Kallfa High performance TFT of a-Si:H on a SiO_2 dielectric 97/98 (1987) 313
Grigorovici, R., see Manaila 97/98 (1987) 195
Grigorovici, R., see Manolescu 97/98 (1987) 519
Grigorovici, R., Closing address 97/98 (1987) 1463
Gross, V., H.W. Grueninger, E. Niemann and R. Fischer, Electronic properties of Ga-doped amorphous silicon 97/98 (1987) 643
Grueninger, H.W., see Gross 97/98 (1987) 643
Grünewald, M. and B. Movaghar, Theory of carrier relaxation in band tails of disordered semiconductors 97/98 (1987) 113
Gu, B., Z. Xu and B. Dong, A theoretical interpretation of thermostimulated conductivity in amorphous semiconductors 97/98 (1987) 479
Guan, X., see Han 97/98 (1987) 595
Guha, S., see Yang 97/98 (1987) 1303
Guha, S., J.S. Payson, S.C. Agarwal and S.R. Ovshinsky, Fluorinated amorphous silicon–germanium alloys deposited from disilane–germane mixture 97/98 (1987) 1455
Guimarães, L., see Martins 97/98 (1987) 1399
Gujrathi, S.C., see Rostaing 97/98 (1987) 1051
Günzel, E., see Karg 97/98 (1987) 1323
Gurman, S.J., see Derbyshire 97/98 (1987) 1103
Gustafson, T.L., R.W. Collins, D.M. Roberts and H. Scher, Charge carrier relaxation in intrinsic hydrogenated amorphous silicon: a systematic investigation of the picosecond decay of photoinduced absorption 97/98 (1987) 121

Hack, M., R.A. Street and M. Shur, Capacitance studies of thermal equilibrium changes in n-type amorphous silicon 97/98 (1987) 803
Hack, M. and M. Shur, Analysis of amorphous silicon thin-film transistors 97/98 (1987) 1291
Hadley, B., M. Green, M. Pollak, R. Chicon and M. Ortuño, Low energy excitations of interacting Anderson localized electrons 97/98 (1987) 233
Hadley, B., see Chicon 97/98 (1987) 237
Haggerty, J.S., see Flint 97/98 (1987) 1419
Haghani, M.A., see Draijer 97/98 (1987) 1287
Hajto, E., P.J.S. Ewen, R. Belford, J. Hajto and A.E. Owen, Optical properties of spin-coated amorphous chalcogenide thin films 97/98 (1987) 1191

Hajto, J., see Hajto 97/98 (1987) 1191
Hajto, J. and I. Janossy, Model for the non-linear intensity dependence of photostructural changes in amorphous semiconductors 97/98 (1987) 1207
Hajto, J., see Choi 97/98 (1987) 1331
Hama, T., see Ohsawa 97/98 (1987) 91
Hamakawa, Y., see Kruangam 97/98 (1987) 293
Hamakawa, Y., see Nitta 97/98 (1987) 695
Hamakawa, Y., see Hattori 97/98 (1987) 879
Hamakawa, Y., see Tsutsumi 97/98 (1987) 1063
Hamakawa, Y., see Hattori 97/98 (1987) 1079
Hamano, T., see Chuang 97/98 (1987) 301
Han, D., see Qiu 97/98 (1987) 587
Han, D., M. Yoshida and K. Morigaki, Light-induced photoluminescence fatigue in a-Si:H 97/98 (1987) 651
Han, D., W. Li, S. Quian and C. Qiu, The density of gap states in single- and multi-layer of a-Si:H measured by optical absorption and infrared stimulated current 97/98 (1987) 751
Han, R., K.L. Ngai, X. Guan and J. Ruvalds, The electron relaxation and photoluminescence decay of the a-Si:H 97/98 (1987) 595
Handlíř, K., see Tichý 97/98 (1987) 1227
Haneman, D., see Durny 97/98 (1987) 927
Harbison, J.P., see Michelson 97/98 (1987) 763
Harbison, J.P., see Cohen 97/98 (1987) 875
Harms, H., see Brunst 97/98 (1987) 1343
Harris, C.J., see Flint 97/98 (1987) 1419
Hasegawa, S., H. Anbutu and Y. Kurata, Bonding properties of amorphous SiN_x:H films with low density of Si–H bonds 97/98 (1987) 1043
Hata, S., see Tsukude 97/98 (1987) 317
Hattori, K., see Nitta 97/98 (1987) 695
Hattori, K., T. Mori, H. Okamoto and Y. Hamakawa, Study of in-plane carrier transport in a-Si:H/a-SiC:H multilayers by transient grating technique 97/98 (1987) 879
Hattori, Y., see Kruangam 97/98 (1987) 293
Hattori, Y., D. Kruangam, T. Toyama, H. Okamoto and Y. Hamakawa, Valency control of p-type a-SiC:H having the optical band gap more than 2.5 eV by electron–cyclotron resonance CVD (ECR CVD) 97/98 (1987) 1079
Hatzopoulos, Z., see Zdetsis 97/98 (1987) 831
Hayama, M., K. Kobayashi, S. Kawamoto, H. Miki and Y. Onishi, Characteristics of a-Si:H films deposited by electron cyclotron resonance plasma CVD 97/98 (1987) 273
Hayano, T., see Imamura 97/98 (1987) 663
Hedges, A.R. and A.D. Caplin, Optical properties of molten chalcogenide iodides of arsenic 97/98 (1987) 1279
Hepburn, A.R., C. Main, J.M. Marshall, C. van Berkel and M.J. Powell, Charge trapping effects in amorphous silicon/silicon nitride thin film transistors 97/98 (1987) 903
Hepp, B., see Essamet 97/98 (1987) 191
Herak, T.V., T.T. Chau, S.R. Mejia, P.K. Shufflebotham, J.J. Schellenberg, H.C. Card, K.C. Kao and R.D. McLeod, Effects of substrate bias on structure and properties of a-Si:H films deposited by ECR microwave plasmas 97/98 (1987) 277
Herion, J., see Foller 97/98 (1987) 567
Herion, J., see Petrova-Koch 97/98 (1987) 807
Herion, J., see Beyer 97/98 (1987) 951

Hilgenberg, B., see Pierz	97/98 (1987)	63
Hirabayashi, I., K. Winer and L. Ley, Photomodulation of the photoelectric yield from a-Si:H	97/98 (1987)	87
Hirose, M. and S. Miyazaki, Quantum wells and superlattices	97/98 (1987)	23
Hirose, M., see Tsukude	97/98 (1987)	317
Hirose, M., see Miyazaki	97/98 (1987)	887
Hishikawa, Y., see Kuwano	97/98 (1987)	289
Hishikawa, Y., K. Watanabe, S. Tsuda, S. Nakano, M. Ohnishi and Y. Kuwano, Variations of the silicon network of amorphous silicon studied by Raman spectroscopy	97/98 (1987)	399
Hoheisel, M., N. Brutscher, H. Oppolzer and S. Schild, The interfaces a-Si:H/Pd and a-Si:H/ITO: structure and electronic properties	97/98 (1987)	959
Hollingsworth, R.E., P.K. Bhat and A. Madan, Microcrystalline and wide band gap p^+ window layers for a-Si p-i-n solar cells	97/98 (1987)	309
Honma, I., H. Hotta, K. Kawai, H. Komiyama and K. Tanaka, The structural stability of reactively-sputtered amorphous multilayer films	97/98 (1987)	947
Hopkinson, M., T.M. Searle, P.G. LeComber and R.A. Gibson, Photoluminescence properties of a-(Si/SiN):H multilayers: a comparison with bulk alloys	97/98 (1987)	883
Hosokawa, Y., see Yamagishi	97/98 (1987)	1355
Hotta, H., see Honma	97/98 (1987)	947
Hoyer, W., see Neumann	97/98 (1987)	1251
Hulin, D., see Fauchet	97/98 (1987)	145
Ichimura, T., see Asano	97/98 (1987)	971
Ihara, Y., see Miyazaki	97/98 (1987)	887
Ilizarov, L.M., see Dembovsky	97/98 (1987)	427
Imagawa, O., see Shimakawa	97/98 (1987)	623
Imamura, S., Y. Kanemitsu, T. Hayano and T. Kitamura, Characterization of deep defect levels in amorphous selenium by optical methods	97/98 (1987)	663
Imura, T., see Myoren	97/98 (1987)	361
Imura, T., see Ueda	97/98 (1987)	1387
Imura, T., see Matsuo	97/98 (1987)	1395
Inokuma, T., see Onari	97/98 (1987)	1115
Ionescu, S., see Popescu	97/98 (1987)	1431
Ishida, S., see Ohsawa	97/98 (1987)	91
Isoya, J., see Yamasaki	97/98 (1987)	691
Itoh, H., see Chuang	97/98 (1987)	301
Ivan, P., see Popescu	97/98 (1987)	1431
Jackson, W.A., see Searle	97/98 (1987)	991
Jackson, W.B., see Chuang	97/98 (1987)	301
Jackson, W.B., see Marshall	97/98 (1987)	563
Jackson, W.B., M.D. Moyer, C.C. Tsai and J. Marshall, Band offsets for the silicon nitride/amorphous silicon interface: implications for charge transport and trapping in silicon nitride	97/98 (1987)	891
Jahn, K., R. Carius and W. Fuhs, Photoluminescence and photoconductivity of a-Si:H at high electric fields	97/98 (1987)	575
Jahn, K., see Liedtke	97/98 (1987)	1083
Jančа, J., see Pajasová	97/98 (1987)	451
Jang, J., see Choi	97/98 (1987)	911
Janossy, I., see Hajto	97/98 (1987)	1207
Jarząbek, B., see Zdanowicz	97/98 (1987)	1203
Jiang, F.S., see Okuda	97/98 (1987)	1351

Joannopoulos, J.D., see Bar-Yam 97/98 (1987) 467
Johnston, R., B. Kramer, J. Masek and L. Schweitzer, The localisation length and the density of states in correlated random systems 97/98 (1987) 241
Jousse, D., see Vaillant 97/98 (1987) 639
Juška, G., K. Arlauskas and E. Montrimas, Features of carriers at very high electric fields in a-Se and a-Si:H 97/98 (1987) 559
Kahnt, H., see Schirrmeister 97/98 (1987) 523
Kakalios, J. and R.A. Street, Thermal equilibrium processes in doped amorphous silicon *(Invited paper)* 97/98 (1987) 767
Kallfa, T., see Griep 97/98 (1987) 313
Kaneko, S. and H. Uchida, Characterization of junctions in a-Si:H image sensors 97/98 (1987) 1359
Kaneko, Y., see Sasano 97/98 (1987) 1295
Kanemitsu, Y., see Imamura 97/98 (1987) 663
Kao, K.C., see Herak 97/98 (1987) 277
Karg, F., E. Günzel and K.v. Klitzing, Dual beam time-of-flight experiments on a-Si:H pπn and pνn diodes 97/98 (1987) 1323
Karpov, V.G., see Baranovskii 97/98 (1987) 487
Kasamura, H., see Matsuishi 97/98 (1987) 1187
Kasner, M., see Weller 97/98 (1987) 229
Kataura, H., see Onari 97/98 (1987) 1115
Katyal, S.C., S. Okano, T. Bando and M. Suzuki, Photo-excited effects in impurity doped double layer chalcogenide films 97/98 (1987) 1195
Kawaguchi, T., S. Maruno and K. Masui, Photobleaching and thermal-bleaching effects in amorphous Ge–S films 97/98 (1987) 1219
Kawai, K., see Honma 97/98 (1987) 947
Kawamoto, S., see Hayama 97/98 (1987) 273
Kawamura, T., see Nakayama 97/98 (1987) 743
Kawamura, T., see Nakayama 97/98 (1987) 1447
Kawazoe, H., Y. Watanabe and M. Yamane, Defects in l- and a-chalcogenides 97/98 (1987) 1255
Kazanskii, A.G., E.P. Milichevich and V.S. Vavilov, Dynamics of Staebler–Wronski effect in hydrogenated amorphous silicon 97/98 (1987) 787
Kempter, K., see Brunst 97/98 (1987) 1343
Kenawy, M.A., M.M. Abd-Elaal, H.A. Zayed and L.I. Soliman, Liquid–crystalline and glassy–crystalline transition of Se–I samples 97/98 (1987) 1275
Kessler, F., see Berner 97/98 (1987) 847
Kessler, F., see Weller 97/98 (1987) 1071
Khait, Yu.L., see Abdulhalim 97/98 (1987) 387
Kim, D.-S., see Tóth 97/98 (1987) 635
Kim, D.-S., see Füstöss-Wégner 97/98 (1987) 1327
Kiriakidis, G., see Zdetsis 97/98 (1987) 831
Kiss, Z., see Böhm 97/98 (1987) 735
Kita, H., see Nakayama 97/98 (1987) 743
Kitamura, T., see Imamura 97/98 (1987) 663
Klapwijk, T.M., see Schropp 97/98 (1987) 1339
Klitzing, K.v., see Karg 97/98 (1987) 1323
Kluge, G., see Ressel 97/98 (1987) 1247
Knights, J.C., see Fedders 97/98 (1987) 357
Knop, R., see Zahorowski 97/98 (1987) 843
Kobayashi, K., see Hayama 97/98 (1987) 273
Koblinger, O., see Santos 97/98 (1987) 859
Kočka, J., M. Vaněček and F. Schauer, a-Si:H gap states investigated by CPM and SCLC *(Invited paper)* 97/98 (1987) 715

Kočka, J., see Schauer 97/98 (1987) 811
Kočka, J., see Lányi 97/98 (1987) 815
Kočka, J., M. Vaněček, M. Nesládek, Q.-D. Tring, J. Stuchlik, O. Stika and A. Triska, Deep states in a-Si:H – changes with light soaking and applied stress 97/98 (1987) 819
Kohda, Y., see Tsukude 97/98 (1987) 317
Kojima, N., see Nitta 97/98 (1987) 1451
Kolobov, A.V., see Bedel'bayeva 97/98 (1987) 1243
Kolodzey, J., see Aljishi 97/98 (1987) 1023
Kolomiets, B.T., see Bedel'bayeva 97/98 (1987) 1243
Komiyama, H., see Honma 97/98 (1987) 947
Kondo, M., see Yamagishi 97/98 (1987) 1355
Konkov, O.I., E.I. Terukov, V.Kh. Kydoyarova and A.A. Babayev, Physical properties of amorphous silicon, prepared by HF silane decomposition at high substrate temperature 97/98 (1987) 1391
Kosarev, A.I., A.A. Andreev, A.V. Zherzdev and A.B. Pevtsov, Features of the behavior of photoluminescence intensity and relaxation in a wide range of temperature for a-Si:H 97/98 (1987) 615
Kosek, F., see Cimpl 97/98 (1987) 439
Kosichkin, Yu.V., see Demishev 97/98 (1987) 1459
Kotkata, M.F., M.H. El-Fouly, M.A. Morsy and S.A. Fayek, A study of thermal analysis of amorphous solid and supercooled liquid selenium–thallium 97/98 (1987) 1259
Koudelka, L., M. Pisárčik, N.I. Krylov and V.A. Ananichev, Short-range order in $Ge_xS_yBr_z$ glassy and liquid samples 97/98 (1987) 1271
Koulmann, J.J., see Muller 97/98 (1987) 1411
Kramer, B., see Johnston 97/98 (1987) 241
Kramer, B., The scaling theory of localization – is it of importance for amorphous semiconductors? *(Organizer's summary)* 97/98 (1987) 253
Krištofik, J., see Rogachev 97/98 (1987) 955
Kruangam, D., T. Toyama, Y. Hattori, M. Deguchi, H. Okamoto and Y. Hamakawa, Improvement of carrier injection efficiency in a-SiC p-i-n LED using highly-conductive wide-gap p,n type a-SiC prepared by ECR CVD 97/98 (1987) 293
Kruangam, D., see Hattori 97/98 (1987) 1079
Krylov, N.I., see Koudelka 97/98 (1987) 1271
Kubler, L., see Bischoff 97/98 (1987) 1407
Kubota, H., see Onuki 97/98 (1987) 1347
Kugler, S. and G. Náray-Szabó, Charge distribution in amorphous silicon clusters. Quantum chemical study combined with ring statistics 97/98 (1987) 503
Kunst, M., see Werner 97/98 (1987) 611
Kunst, M., see Werner 97/98 (1987) 791
Kurata, Y., see Hasegawa 97/98 (1987) 1043
Kuroda, S., see Yamasaki 97/98 (1987) 691
Kusian, W., H. Pfleiderer and B. Bullemer, Spectral photocurrent–voltage characteristics of a-Si pνn and pπn diodes 97/98 (1987) 647
Kuwano, Y., H. Tarui, T. Takahama, M. Nishikuni, Y. Hishikawa, N. Nakamura, S. Tsuda, S. Nakano and M. Ohnishi, High efficiency a-Si solar cells with a superlattice structure p-layer and stable a-Si solar cells with reduced Si–H_2 bond density 97/98 (1987) 289
Kuwano, Y., see Hishikawa 97/98 (1987) 399
Kydoyarova, V.Kh., see Konkov 97/98 (1987) 1391

Lagarde, P., see Flank 97/98 (1987) 435

Landweer, G., R. Schreutelkamp, H. Simons, J. Bezemer and W.F. van der Weg, Determination of the density of states in amorphous silicon from thermostimulated conductivity measurements 97/98 (1987) 711
Lannin, J.S., Structural order and dynamics of amorphous Si and Ge 97/98 (1987) 39
Lannin, J.S., Intermediate range order in elemental amorphous and liquid semiconductors 97/98 (1987) 203
Lányi, Š., V. Nádaždy and J. Kočka, Instability of gap states in phosphorus doped a-Si:H, demonstrated in DLTS 97/98 (1987) 815
Larchev, V.I., see Demishev 97/98 (1987) 1459
Le Contellec, M., F. Maurice, J. Richard, B. Vinouze and F. Richou, Very simple a-Si:H TFT fabrication process for LCD-TV application 97/98 (1987) 297
LeComber, P., see Spear 97/98 (1987) 15
LeComber, P.G., Focused session on device physics *(Organizer's summary)* 97/98 (1987) 325
LeComber, P.G., see Djamdji 97/98 (1987) 543
LeComber, P.G., see Hopkinson 97/98 (1987) 883
LeComber, P.G., B. Dunnett, W.E. Spear and R. Gibson, Substitutional and interstitial doping of amorphous silicon nitride 97/98 (1987) 1003
LeComber, P.G., see Choi 97/98 (1987) 1331
Lee, C., see Choi 97/98 (1987) 911
Lee, J.M., see Pfeiffer 97/98 (1987) 379
Lee, J.M., see Yang 97/98 (1987) 1119
Lee, J.M. and M.A. Paesler, Kinetics of laser-induced phenomena in glassy As_2S_3 97/98 (1987) 1235
Lenzner, M., see Bergner 97/98 (1987) 1335
Leopold, D.J., see Fedders 97/98 (1987) 357
Leta, D., see Abeles 97/98 (1987) 353
Levine, J., see Chuang 97/98 (1987) 301
Ley, L., see Hirabayashi 97/98 (1987) 87
Ley, L., see Walloch 97/98 (1987) 699
Ley, L., see Winer 97/98 (1987) 703
Ley, L., see Santos 97/98 (1987) 859
Ley, L., see Bell 97/98 (1987) 1007
Li, K.D., see Fauchet 97/98 (1987) 1267
Li, W., see Han 97/98 (1987) 751
Li, Y.M., see Chahed 97/98 (1987) 727
Li, Y.M., see MacKenzie 97/98 (1987) 1019
Li, Z., see Chen 97/98 (1987) 341
Li, Z., see Feng 97/98 (1987) 915
Liedtke, S., K. Jahn, F. Finger and W. Fuhs, Defects and recombination in a-$Si_{1-x}C_x$:H films 97/98 (1987) 1083
Lin, Z., see Peng 97/98 (1987) 899
Lisitsa, M.P., I.D. Turjanitsa and I.V. Fekeshgazi, Non-linear light absorption in Sb–S–I glasses 97/98 (1987) 1159
Liu, H., see Feng 97/98 (1987) 915
Liu, J., see Su 97/98 (1987) 1363
Liu, J.Z. and P.C. Taylor, Photodarkening effect in $Cu_x(As_{0.4}Se_{0.6})_{1-x}$ and $Cu_x(As_{0.4}S_{0.6})_{1-x}$ 97/98 (1987) 1123
Liu, Z., see Zhang 97/98 (1987) 1311
Long, A.R., see Shimakawa 97/98 (1987) 623
Longeaud, C., see Vanderhaghen 97/98 (1987) 1059
Losch, W., see Beyer 97/98 (1987) 951
Lotter, E., see Weller 97/98 (1987) 1071
Lucovsky, G., Specification of medium range order in amorphous materials 97/98 (1987) 155
Lucovsky, G. and D.V. Tsu, Differences between direct and remote plasma enhanced CVD 97/98 (1987) 265

Lucovsky, G., see Tsu 97/98 (1987) 839
Lucovsky, G., see Wong 97/98 (1987) 1171
Lucovsky, G., see Parsons 97/98 (1987) 1375
Lüder, E., see Griep 97/98 (1987) 313
Lukeš, F., see Cimpl 97/98 (1987) 439
Lyapin, A.G., see Demishev 97/98 (1987) 1459
Lyubin, V.M., Photostructural changes in chalcogenide glasses 97/98 (1987) 47
Lyubin, V.M., see Bedel'bayeva 97/98 (1987) 1243

Maçarico, A., see Martins 97/98 (1987) 1399
Mackay, A.L., Quasi-crystals and amorphous materials 97/98 (1987) 55
MacKenzie, K.D., see Chahed 97/98 (1987) 727
MacKenzie, K.D., J.H. Burnett, J.R. Eggert, Y.M. Li and W. Paul, Improvement of photoconductive response in amorphous silicon–germanium alloys produced from fluorides instead of hydrides 97/98 (1987) 1019
MacKenzie, K.D. and W. Paul, Transient and steady-state photoconductivity in a-$Si_{1-x}Ge_x$:H,F alloys 97/98 (1987) 1055
Macovei, D., see Manolescu 97/98 (1987) 519
Madan, A., see Hollingsworth 97/98 (1987) 309
Main, C., J. Berkin, R. Russell, A. Merazga and J.M. Marshall, Trapping, recombination, and metastable states in n-type α-Si:H 97/98 (1987) 779
Main, C., see Hepburn 97/98 (1987) 903
Majkrzak, C., see Abeles 97/98 (1987) 353
Maksimova, S.Ya., see Sarsembinov 97/98 (1987) 987
Málek, J., see Drchal 97/98 (1987) 199
Maloufi, N., see Por 97/98 (1987) 419
Manaila, R. and R. Grigorovici, Surface reconstruction in amorphous solids 97/98 (1987) 195
Manaila, R., see Manolescu 97/98 (1987) 519
Manolescu, A., D. Macovei, R. Manaila, R. Grigorovici and P. Pausescu, Effect of s-p-d hybridization on the EXAFS phase-shifts in amorphous germanium 97/98 (1987) 519
Mao, G., see Chen 97/98 (1987) 341
Marchal, G., see Por 97/98 (1987) 419
Mareš, J.J., see Rogachev 97/98 (1987) 955
Maris, H.J., see Grahn 97/98 (1987) 855
Mariucci, L., F. Ferrazza, D. Della Sala, M. Capizzi, F. Evangelisti and U. Coscia, a-$Si_{1-x}Ge_x$:H alloys for solar cells 97/98 (1987) 1075
Marshall, J., see Jackson 97/98 (1987) 891
Marshall, J.M., R.A. Street, M.J. Thompson and W.B. Jackson, The energy distribution of localised states, and the mobilities of free carriers in a-Si:H, from time of flight and other measurements 97/98 (1987) 563
Marshall, J.M., see Main 97/98 (1987) 779
Marshall, J.M., see Hepburn 97/98 (1987) 903
Martins, R., N. Carvalho, E. Fortunato, A. Maçarico, M. Santos, I. Baia, M. Vieira and L. Guimarães, Effects of U.V. light on the transport properties of a-Si:H films during their growth 97/98 (1987) 1399
Maruno, S., see Kawaguchi 97/98 (1987) 1219
Masek, J., see Johnston 97/98 (1987) 241
Mašek, J., see Wilke 97/98 (1987) 491
Masui, K., see Kawaguchi 97/98 (1987) 1219
Matshushita, T., see Okuda 97/98 (1987) 1351
Matsuda, A. and K. Tanaka, Guiding principle for preparing highly photosensitive Si-based amorphous alloys *(Invited paper)* 97/98 (1987) 1367

Matsuishi, K., H. Kasamura, S. Onari and T. Arai, Far infrared absorption spectra of chalcogenide amorphous semiconductors and the spatial charge fluctuation 97/98 (1987) 1187
Matsumaru, H., see Sasano 97/98 (1987) 1295
Matsumura, H., Catalytic chemical vapor deposition method to obtain high quality amorphous silicon and silicon–germanium 97/98 (1987) 1379
Matsumura, M., S. Sekine, J. Yue and Y. Takeuchi, Device physics of a-Si:H charge-coupled devices 97/98 (1987) 1299
Matsuo, S., M. Ueda, T. Imura and Y. Osaka, Effect of hydrogen dilution on structure of a-Si:H prepared by substrate impedance tuning technique 97/98 (1987) 1395
Matsushita, T., see Naito 97/98 (1987) 1231
Matsuura, H., H. Okushi and K. Tanaka, Schottky barrier junctions of hydrogenated amorphous silicon–germanium alloys 97/98 (1987) 963
Matz, W., see Neumann 97/98 (1987) 1251
Maurice, F., see Le Contellec 97/98 (1987) 297
McDowell, A., see Sette 97/98 (1987) 895
McLeod, R.D., see Herak 97/98 (1987) 277
Meaudre, M., see Meaudre 97/98 (1987) 799
Meaudre, R. and M. Meaudre, Influence of metastable dangling bonds and donors on the D.C. conductivity of hydrogenated amorphous silicon 97/98 (1987) 799
Mebert, J., see Santos 97/98 (1987) 859
Mejia, S.R., see Herak 97/98 (1987) 277
Mell, H., see Pierz 97/98 (1987) 63
Mendoza, D., see Pickin 97/98 (1987) 599
Menelle, A., Medium range order models of a-Si:H and small angle neutron scattering 97/98 (1987) 337
Merazga, A., see Main 97/98 (1987) 779
Mertens, R., see Symons 97/98 (1987) 1315
Michelson, C.E., J.D. Cohen and J.P. Harbison, Capacitance studies of ion-implanted n-type hydrogenated amorphous silicon 97/98 (1987) 763
Michelson, C.E., see Cohen 97/98 (1987) 875
Migus, A., see Fauchet 97/98 (1987) 145
Miki, H., see Hayama 97/98 (1987) 273
Milichevich, E.P., see Kazanskii 97/98 (1987) 787
Misrar, A., J.-M. Saiter and C. Vautier, Dark conductivity of amorphous $Ge_{0.08}Te_{0.92}$ thin films 97/98 (1987) 671
Miyazaki, S., see Hirose 97/98 (1987) 23
Miyazaki, S., see Tsukude 97/98 (1987) 317
Miyazaki, S., Y. Ihara and M. Hirose, Structural stability of amorphous semiconductor superlattices 97/98 (1987) 887
Mizushima, K., see Morimoto 97/98 (1987) 943
Mobilio, S. and A. Filipponi, EXAFS in amorphous silicon alloys *(Invited paper)* 97/98 (1987) 365
Mobilio, S., see Filipponi 97/98 (1987) 403
Möbius, A., The metal–semiconductor transition in three-dimensional disordered systems – reanalysis of recent experiments for and against minimum metallic conductivity 97/98 (1987) 225
Möbius, A. and M. Richter, Density of states within the Coulomb gap 97/98 (1987) 483
Mohr, R., see Yang 97/98 (1987) 1303
Mohring, H.-D., M.B. Schubert, G. Schumm and G.H. Bauer, Electronic and optical effects of boron doping by plasma assisted diffusion in a-SiC:H 97/98 (1987) 1415
Montrimas, E., see Juška 97/98 (1987) 559
Mori, K., H. Okushi and K. Tanaka, Energy level of neutral dangling-bond center (D^0) in undoped a-Si:H determined by isothermal capacitance transient spectroscopy under high temperature 97/98 (1987) 723

Mori, T., see Hattori 97/98 (1987) 879
Morigaki, K., see Yokomichi 97/98 (1987) 67
Morigaki, K., see Yoshida 97/98 (1987) 579
Morigaki, K., see Han 97/98 (1987) 651
Morigaki, K., see Ogihara 97/98 (1987) 867
Morigaki, K., see Yamaguchi 97/98 (1987) 931
Morimoto, A., K. Mizushima and T. Shimizu, a-Si:H/ZnS superlattice 97/98 (1987) 943
Morsy, M.A., see Kotkata 97/98 (1987) 1259
Mosseri, R., see Cuniot 97/98 (1987) 171
Mosseri, R. and J.P. Gaspard, Effect of wrong bonds on the electronic structure of amorphous III–V alloys 97/98 (1987) 415
Mott, N.F., Physical aspects of localization 97/98 (1987) 213
Mott, N.F., Conduction at a mobility edge *(Invited paper)* 97/98 (1987) 531
Movaghar, B., see Grünewald 97/98 (1987) 113
Moyer, M.D., see Jackson 97/98 (1987) 891
Mui, K. and F.W. Smith, The effect of interface alloying on the optical absorption of a-Si:H/a-Si_xN_{1-x}:H multilayers 97/98 (1987) 975
Mui, K., D.K. Basa, R. Corderman and F.W. Smith, Optical constants and microstructure of amorphous hydrogenated silicon–carbon alloy films 97/98 (1987) 999
Muller, D., F. Ringeisen, D. Bolmont and J.J. Koulmann, Hydrogenation of amorphized silicon studied by UPS 97/98 (1987) 1411
Munz, P., see Berner 97/98 (1987) 847
Murayama, K., Hot photoluminescence in chalcogenide glasses 97/98 (1987) 1147
Murayama, K., see Yamaguchi 97/98 (1987) 1199
Muschik, T., see Schwarz 97/98 (1987) 759
Myoren, H., P. Shrestha, T. Imura and Y. Osaka, Characterization of the structure in hydrogenated amorphous silicon by means of ^{119}Sn Mössbauer spectroscopy 97/98 (1987) 361

Nádaždy, V., see Lányi 97/98 (1987) 815
Nagels, P., see Adriaenssens 97/98 (1987) 675
Naito, H., T. Termiane, M. Okuda and T. Matsushita, Photo-induced phenomena in transport properties of a-As_2Se_3 97/98 (1987) 1231
Nakamura, N., see Kuwano 97/98 (1987) 289
Nakano, M., see Nakayama 97/98 (1987) 1447
Nakano, S., see Kuwano 97/98 (1987) 289
Nakano, S., see Hishikawa 97/98 (1987) 399
Nakayama, T., see Yamagishi 97/98 (1987) 1355
Nakayama, Y., H. Kita, T. Takahashi, S. Akita and T. Kawamura, Dark decay of surface potential: measurement of the density of localized states in highly resistive amorphous silicon alloys 97/98 (1987) 743
Nakayama, Y., S. Akita, M. Nakano and T. Kawamura, High-rate deposition of photosensitive a-SiC:H using a carbon source of C_2H_2 97/98 (1987) 1447
Náray-Szabó, G., see Kugler 97/98 (1987) 503
Navrátil, K., see Pajasová 97/98 (1987) 451
Nebel, C.E., see Weller 97/98 (1987) 1071
Nenciu, A., see Popescu 97/98 (1987) 1431
Nesládek, M., see Schauer 97/98 (1987) 811
Nesládek, M., see Kočka 97/98 (1987) 819
Neumann, H., W. Hoyer, W. Matz and M. Wobst, Temperature dependence of the structure of liquid eutectic Ge–Te alloys 97/98 (1987) 1251
Ngai, K.L., see Han 97/98 (1987) 595
Nichols, C.S., L.H. Yang and C.Y. Fong, The doping mechanism in amorphous silicon 97/98 (1987) 495

Nicolae, M., see Popescu 97/98 (1987) 1431
Niemann, E., see Gross 97/98 (1987) 643
Nijs, J., see Symons 97/98 (1987) 1315
Ninomiya, T., see Yamaguchi 97/98 (1987) 1199
Nishikuni, M., see Kuwano 97/98 (1987) 289
Nitta, S., see Yamaguchi 97/98 (1987) 931
Nitta, S., S. Nonomura, R. Takagi, N. Kojima and A. Yasuda, Deposition condition of hydrogenated amorphous carbon films having quasi-onedimensional structures 97/98 (1987) 1451
Nitta, Y., K. Abe, K. Hattori, H. Okamoto and Y. Hamakawa, Energetic distribution of dangling bond states in undoped amorphous silicon 97/98 (1987) 695
Nitta, Y., see Tsutsumi 97/98 (1987) 1063
Noll, G. and E.O. Göbel, Picosecond photoinduced index changes in a-Si:H and related alloys measured by transient grating experiments 97/98 (1987) 141
Noll, G., see Fischer 97/98 (1987) 591
Nonomura, S., see Yamaguchi 97/98 (1987) 931
Nonomura, S., see Nitta 97/98 (1987) 1451
Norberg, R.E., see Fedders 97/98 (1987) 357
Norman, D., see Sette 97/98 (1987) 895
Nosé, S., see Yonezawa 97/98 (1987) 373
Nowick, W., see Bergner 97/98 (1987) 1335

Ogihara, C., H. Ohta, M. Yamaguchi, H. Takenaka and K. Morigaki, Time-resolved optically detected magnetic resonance in a-Si:H/a-$Si_{1-x}N_x$:H superlattices 97/98 (1987) 867
Ogihara, C., see Yamaguchi 97/98 (1987) 931
Ohnishi, M., see Kuwano 97/98 (1987) 289
Ohnishi, M., see Hishikawa 97/98 (1987) 399
Ohsawa, M., T. Hama, T. Akasaka, H. Sakai, S. Ishida and Y. Uchida, Creation and saturation of light-induced defects in a-Si:H 97/98 (1987) 91
Ohsawa, M., see Asano 97/98 (1987) 971
Ohta, H., see Ogihara 97/98 (1987) 867
Ohta, H., see Yamaguchi 97/98 (1987) 931
Okamoto, H., see Kruangam 97/98 (1987) 293
Okamoto, H., see Nitta 97/98 (1987) 695
Okamoto, H., see Hattori 97/98 (1987) 879
Okamoto, H., see Tsutsumi 97/98 (1987) 1063
Okamoto, H., see Hattori 97/98 (1987) 1079
Okano, S., see Katyal 97/98 (1987) 1195
Okuda, M., see Naito 97/98 (1987) 1231
Okuda, M., F.S. Jiang, J.C. Rhee and T. Matshushita, Erasable laser recording characteristics in a Ga–Se–Te optical disk medium 97/98 (1987) 1351
Okushi, H. and K. Tanaka, Energy level and photoionization cross section of gap states in a-Si:H 97/98 (1987) 75
Okushi, H., see Mori 97/98 (1987) 723
Okushi, H., see Matsuura 97/98 (1987) 963
Olszakier, M., see Vardeny 97/98 (1987) 109
Omeljanovsky, E.M., see Balagurov 97/98 (1987) 527
Onari, S., T. Inokuma, H. Kataura and T. Arai, Absorption edge of the amorphous $(GeS_2)_x(As_2S_3)_{1-x}$ and $(GeSe_2)_x(As_2Se_3)_{1-x}$ systems under hydrostatic pressure 97/98 (1987) 1115
Onari, S., see Matsuishi 97/98 (1987) 1187
Onishi, Y., see Hayama 97/98 (1987) 273
Onmori, R.K., see Pereyra 97/98 (1987) 871

Onuki, M., K. Tsubusaki and H. Kubota, AC photoconductivity of amorphous GaP diodes made by reactive evaporation under implantation of hydrogen ions 97/98 (1987) 1347
Oppolzer, H., see Hoheisel 97/98 (1987) 959
O'Reilly, E.P., The electronic structure of amorphous carbon *(Invited paper)* 97/98 (1987) 1095
Ortuño, M., see Hadley 97/98 (1987) 233
Ortuño, M., see Chicon 97/98 (1987) 237
Osaka, Y., see Myoren 97/98 (1987) 361
Osaka, Y., see Ueda 97/98 (1987) 1387
Osaka, Y., see Matsuo 97/98 (1987) 1395
Ott, K., see Draijer 97/98 (1987) 1287
Overhof, H., The prefactor of the DC conductivity in amorphous semiconductors 97/98 (1987) 539
Ovshinsky, S.R., see Guha 97/98 (1987) 1455
Owen, A.E., see Ewen 97/98 (1987) 1127
Owen, A.E., see Hajto 97/98 (1987) 1191
Owen, A.E., see Choi 97/98 (1987) 1331
Ozawa, T., see Chuang 97/98 (1987) 301

Paasche, S.M., see Berner 97/98 (1987) 847
Paasche, S.M., see Weller 97/98 (1987) 1071
Paesler, M.A., see Pfeiffer 97/98 (1987) 379
Paesler, M.A., see Yang 97/98 (1987) 1119
Paesler, M.A., see Yang 97/98 (1987) 1151
Paesler, M.A., see Lee 97/98 (1987) 1235
Pajasová, L., J. Zemek, J. Janča and K. Navrátil, Optical, electrical, mechanical and photoelectronic properties of hard amorphous carbon films 97/98 (1987) 451
Pak, H.-S., see Tóth 97/98 (1987) 635
Pak, H.-S., see Füstöss-Wégner 97/98 (1987) 1327
Pantelides, S.T., Gap states in amorphous silicon – dangling and floating bonds 97/98 (1987) 79
Pantelides, S.T., Defect dynamics and the properties of amorphous silicon 97/98 (1987) 463
Paparazzo, E., see Quaresima 97/98 (1987) 979
Park, J.W., see Turner 97/98 (1987) 1307
Parker, M.A. and E.A. Schiff, The geometry problem for photocarrier drift mobilities in a-Si:H 97/98 (1987) 627
Parsons, G.N., D.V. Tsu and G. Lucovsky, Optical and electrical properties of a-Si:H films grown by remote plasma enhanced chemical vapor deposition (RPECVD) 97/98 (1987) 1375
Patella, F., see Evangelisti 97/98 (1987) 407
Paul, W., see Chahed 97/98 (1987) 727
Paul, W., see MacKenzie 97/98 (1987) 1019
Paul, W., see MacKenzie 97/98 (1987) 1055
Paulick, C.A., see Draijer 97/98 (1987) 1287
Pausescu, P., see Manolescu 97/98 (1987) 519
Payson, J.S., see Van Oort 97/98 (1987) 1427
Payson, J.S., see Guha 97/98 (1987) 1455
Pellegatti, A., see Bellissent 97/98 (1987) 1263
Peng, S., Z. Su and Z. Lin, Internal photoemission studies on M/a-Si:H interface 97/98 (1987) 899
Peng, S., see Su 97/98 (1987) 1363
Pereyra, I., M.N.P. Carreno, R.K. Onmori, C.A. Sassaki, A.M. Andrade and F. Alvarez, Evidence of quantum size effects in a-Si:H/a-SiC_x:H superlattices. Observation of negative resistance in double barrier structures 97/98 (1987) 871

Perfetti, P., see Evangelisti 97/98 (1987) 407
Perfetti, P., see Quaresima 97/98 (1987) 979
Perluzzo, G., see Barclay 97/98 (1987) 603
Perrin, J. and B. Allain, Surface reactions of radicals during deposition of amorphous semiconductors by photochemical decomposition of molecular hydrides 97/98 (1987) 261
Perry, J.W., see Bhat 97/98 (1987) 1383
Petrova-Koch, V., H.P. Zeindl, J. Herion and W. Beyer, Fast hydrogen diffusion in amorphous silicon 97/98 (1987) 807
Petukhov, A.G., see Balagurov 97/98 (1987) 527
Pevtsov, A.B., see Kosarev 97/98 (1987) 615
Pfeiffer, G., M.A. Paesler and J.M. Lee, Modelling the structure of amorphous As_2S_3: Helical structures and a lack of planarity 97/98 (1987) 379
Pfleiderer, H., see Kusian 97/98 (1987) 647
Pickin, W., D. Mendoza and J.C. Alonso, Transient photoconductivity studies in a-Si:H 97/98 (1987) 599
Pieczonková, A., see Velický 97/98 (1987) 455
Pierz, K., B. Hilgenberg, H. Mell and G. Weiser, Gap-state distribution in n-type and p-type a-Si:H from optical absorption 97/98 (1987) 63
Piggins, N., E.A. Davis and S.C. Bayliss, Optical properties and spin densities of SiN_x(:H) films 97/98 (1987) 1047
Pirogov, F.V. and K.K. Shvarts, The mechanism of high-temperature photostructural transformation in low dimensional systems 97/98 (1987) 1211
Pisárčik, M., see Koudelka 97/98 (1987) 1271
Pogány, L., see Füstöss-Wégner 97/98 (1987) 1327
Polcer, J., see Salyk 97/98 (1987) 1435
Pollak, M., see Hadley 97/98 (1987) 233
Pollak, M., see Chicon 97/98 (1987) 237
Pollak, M., see Talamantes 97/98 (1987) 555
Pompe, W., see Richter 97/98 (1987) 1443
Popescu, C., T. Stoica, A. Dragomir, A. Nenciu, M. Nicolae, P. Ivan and S. Ionescu, GD amorphous silicon obtained from trichlorsilane 97/98 (1987) 1431
Popescu, M., Atomic-scale structure of amorphous and liquid sulphur 97/98 (1987) 187
Popova, S.V., see Demishev 97/98 (1987) 1459
Por, A., A. Audouard, N. Maloufi, G. Marchal and M. Gerl, Structural relaxation in amorphous Si_xSn_{1-x} semiconductors 97/98 (1987) 419
Poulain, S., see Rostaing 97/98 (1987) 1051
Powell, M.J., C. van Berkel and I.D. French, The resolution of a-Si thin film transistor instability mechanisms 97/98 (1987) 321
Powell, M.J., see Hepburn 97/98 (1987) 903
Price, D.L., S. Susman and A.C. Wright, Probing medium-range order in chalcogenide glasses by neutron scattering and optical spectroscopy 97/98 (1987) 167
Prieto, P., see Alvarez 97/98 (1987) 1319
Prikhodko, O.Yu., see Sarsembinov 97/98 (1987) 987
Proust, N., see Essamet 97/98 (1987) 191

Qi, M.-W., see Wang 97/98 (1987) 1039
Qian, S., see Qiu 97/98 (1987) 587
Qiu, C., S. Qian and D. Han, Transient behaviour of photoconductivity of a-Si:H in dual beam measurements 97/98 (1987) 587
Qiu, C., see Han 97/98 (1987) 751
Quaresima, C., see Evangelisti 97/98 (1987) 407
Quaresima, C., P. Perfetti, E. Paparazzo, M. Capozi, C. Vaccarezza, B. Russo and C. Coluzza, Effect of hydrogen on SiO_x and SiO_x–Si interface 97/98 (1987) 979

Quian, S., see Han 97/98 (1987) 751
Quitmann, D., see Draijer 97/98 (1987) 1287

Ranganathan, R. and P.C. Taylor, Subgap absorption in a-Si:H using photoluminescence absorption spectroscopy (PLAS) 97/98 (1987) 707
Ready, S.E., see Boyce 97/98 (1987) 345
Redfield, D., Thermal creation of metastable defects in a-Si:H 97/98 (1987) 783
Rennie, J.H.S. and S.R. Elliott, Investigations of the mechanism of photodissolution of silver in amorphous germanium chalcogenide thin films 97/98 (1987) 1239
Ressel, R., G. Kluge and P. Süptitz, Investigation of photodoping kinetics in amorphous Ge-chalcogenides 97/98 (1987) 1247
Reynolds, S., see Choi 97/98 (1987) 1331
Rhee, J.C., see Okuda 97/98 (1987) 1351
Richard, J., see Le Contellec 97/98 (1987) 297
Richardson, C.H., see Sette 97/98 (1987) 895
Richou, F., see Le Contellec 97/98 (1987) 297
Richter, A. and W. Pompe, Laser plasma deposition and film structure of covalently bound materials 97/98 (1987) 1443
Richter, M., see Möbius 97/98 (1987) 483
Ringeisen, F., see Muller 97/98 (1987) 1411
Ristein, J., see Weiser 97/98 (1987) 1131
Ritter, D., E. Zeldov and K. Weiser, Diffusion length measurements in a-Si:H using the steady state photocarrier grating technique 97/98 (1987) 571
Ritter, D., E. Zeldov and K. Weiser, Ambipolar transport in amorphous semiconductors in the relaxation regime 97/98 (1987) 619
Roberts, D.M., see Gustafson 97/98 (1987) 121
Robertson, J., Theory of band lineups in amorphous semiconductor heterojunctions 97/98 (1987) 863
Robino, M., see Deiss 97/98 (1987) 679
Rogachev, N.A., V. Šmíd, J.J. Mareš and J. Krištofik, Amorphous nickel silicides prepared by magnetron co-sputtering 97/98 (1987) 955
Rosan, K.H., see Brunst 97/98 (1987) 1343
Rose, M.J., see Choi 97/98 (1987) 1331
Ross, R., see Yang 97/98 (1987) 1303
Rosso, M., see Thomas 97/98 (1987) 755
Rostaing, J.C., Y. Cros, S.C. Gujrathi and S. Poulain, Quantitative infrared characterization of plasma enhanced CVD silicon oxynitride films 97/98 (1987) 1051
Rudenko, A.I., see Arkhipov 97/98 (1987) 129
Russell, R., see Main 97/98 (1987) 779
Russo, B., see Quaresima 97/98 (1987) 979
Ruvalds, J., see Han 97/98 (1987) 595

Saiter, J.-M., see Misrar 97/98 (1987) 671
Sakai, H., see Ohsawa 97/98 (1987) 91
Sakai, H., see Asano 97/98 (1987) 971
Sakamoto, S., see Yonezawa 97/98 (1987) 373
Sakata, S., see Tsutsumi 97/98 (1987) 1063
Salamon, S., see Böhm 97/98 (1987) 735
Salyk, O., F. Schauer, O. Zmeškal, P. Sládek, K. Zubík and J. Polcer, Amorphous hydrogenated silicon prepared by ion beam assisted reactive evaporation – preparation and basic properties 97/98 (1987) 1435
Sansores, E., see Barrio 97/98 (1987) 499

Santos, M., see Martins 97/98 (1987) 1399
Santos, P.V., L. Ley, J. Mebert and O. Koblinger, Frequency gaps for zone-folded acoustic phonons in amorphous superlattices 97/98 (1987) 859
Sarr, M., see Barclay 97/98 (1987) 687
Sarsembinov, Sh.Sh., O.Yu. Prikhodko, S.Ya. Maksimova, S.A. Dzakelov and V.L. Averyanov, Electrical and photoelectrical properties of crystalline semiconductor–ChVS heterojunction controlled by ChVS modification 97/98 (1987) 987
Sasano, A., H. Matsumaru, Y. Kaneko and T. Tsukada, Phosphorus diffusion effect on off-current of a-Si thin film transistors 97/98 (1987) 1295
Sassaki, C.A., see Pereyra 97/98 (1987) 871
Sauer, B., see Draijer 97/98 (1987) 1287
Sawan, Y., see Wang 97/98 (1987) 631
Sayers, D.E., see Yang 97/98 (1987) 1119
Sayers, D.E., see Yang 97/98 (1987) 1151
Schauer, F., see Kocka 97/98 (1987) 715
Schauer, F. and O. Zmeškal, The bulk electron states spectroscopy by temperature-modulated space-charge-limited currents (TM-SCLC) 97/98 (1987) 747
Schauer, F., O. Zmeškal, M. Nesládek and J. Kočka, Stable and metastable states in phosphorus-doped a-Si:H by temperature-modulated space-charge-limited current (TM-SCLC) method 97/98 (1987) 811
Schauer, F., see Salyk 97/98 (1987) 1435
Schellenberg, J.J., see Herak 97/98 (1987) 277
Scher, H., see Gustafson 97/98 (1987) 121
Schiff, E.A., see Parker 97/98 (1987) 627
Schild, S., see Hoheisel 97/98 (1987) 959
Schirrmeister, F., H. Kahnt and A. Feltz, Frequency dependent conductivity and the time distribution function of hopping events 97/98 (1987) 523
Schmidt, M.P., see Solomon 97/98 (1987) 1091
Schneider, U., B. Schröder and F. Finger, The creation of metastable defects in a-Si:H films by high dose irradiation with keV-electrons 97/98 (1987) 795
Schreiber, M., Numerical investigation of the Anderson transition 97/98 (1987) 221
Schreutelkamp, R., see Landweer 97/98 (1987) 711
Schröder, B., see Schneider 97/98 (1987) 795
Schropp, R.E.I., A.J. Boonstra and T.M. Klapwijk, Reversible dangling-bond generation in amorphous silicon thin-film transistors 97/98 (1987) 1339
Schubert, M.B., see Mohring 97/98 (1987) 1415
Schumacher, R., see Djamdji 97/98 (1987) 543
Schumm, G., see Mohring 97/98 (1987) 1415
Schwartz, R.J., see Turner 97/98 (1987) 1307
Schwarz, R., S. Goedecker, T. Muschik, N. Wyrsch, A.V. Shah and H. Curtins, Measurement of surface photovoltage in high-rate deposited a-Si:H films and comparison with photothermal deflection spectroscopy and conductivity data 97/98 (1987) 759
Schweitzer, L., see Johnston 97/98 (1987) 241
Searle, T.M., see Hopkinson 97/98 (1987) 883
Searle, T.M., W.A. Jackson and I.G. Austin, Optical properties of amorphous Si:N:H alloys *(Invited paper)* 97/98 (1987) 991
Sekine, S., see Matsumura 97/98 (1987) 1299
Sekiya, T., see Watanabe 97/98 (1987) 667
Seleznev, V.N., see Agafonov 97/98 (1987) 827
Senemaud, C., see Godet 97/98 (1987) 431
Senemaud, C., see Solomon 97/98 (1987) 1091
Senemaud, C., see Theye 97/98 (1987) 1107

Sette, F., B. Abeles, L. Yang, A. McDowell, D. Norman and C.H. Richardson, Structure of hydrogenated Si–Ge and Si–SiN_x amorphous semiconductors heterojunctions 97/98 (1987) 895
Seynhaeve, G., see Adriaenssens 97/98 (1987) 133
Seynhaeve, G., see Barclay 97/98 (1987) 603
Seynhaeve, G., R.P. Barclay and G.J. Adriaenssens, Influence of light absorption depth in transient photocurrent experiments 97/98 (1987) 607
Seynhaeve, G., see Adriaenssens 97/98 (1987) 675
Shah, A.V., see Favre 97/98 (1987) 731
Shah, A.V., see Schwarz 97/98 (1987) 759
Shen, D.S., see Conde 97/98 (1987) 939
Shen, D.S., see Aljishi 97/98 (1987) 1023
Shimakawa, K., A.R. Long, M.J. Anderson and O. Imagawa, Frequency dependent loss in glow discharge amorphous silicon 97/98 (1987) 623
Shimizu, I., Reactions on substrate for preparation of silicon-networks from precursors, SiF_nH_m $(n+m<3)$ 97/98 (1987) 257
Shimizu, I., see Shirai 97/98 (1987) 1035
Shimizu, T., see Morimoto 97/98 (1987) 943
Shing, Y.H., see Bhat 97/98 (1987) 1383
Shirafuji, J., see Shirakawa 97/98 (1987) 967
Shirai, H. and I. Shimizu, Transport and relaxation properties of photo-induced carriers in amorphous Si-based films with artificial potential structure 97/98 (1987) 1035
Shirakawa, K. and J. Shirafuji, Photoelectric characterization of interface between a-Si:H and a-SiN_x:H 97/98 (1987) 967
Shklovskii, B.I., see Efros 97/98 (1987) 31
Shklovskii, B.I., see Baranovskii 97/98 (1987) 487
Shrestha, P., see Myoren 97/98 (1987) 361
Shufflebotham, P.K., see Herak 97/98 (1987) 277
Shur, M., see Hack 97/98 (1987) 803
Shur, M., see Hack 97/98 (1987) 1291
Shutov, S.D., see Arkhipov 97/98 (1987) 129
Shvarts, K.K., see Pirogov 97/98 (1987) 1211
Silver, M. and V. Cannella, A simplified analytic model for double injection applied to amorphous silicon alloys 97/98 (1987) 305
Silver, M., see Wang 97/98 (1987) 631
Silver, M., see Branz 97/98 (1987) 655
Simons, H., see Landweer 97/98 (1987) 711
Skrotskaya, G.G., see Demishev 97/98 (1987) 1459
Sládek, P., see Salyk 97/98 (1987) 1435
Slobodin, D., see Aljishi 97/98 (1987) 1023
Sluchanko, N.E., see Demishev 97/98 (1987) 1459
Šmíd, V., see Rogachev 97/98 (1987) 955
Smith, F.W., see Mui 97/98 (1987) 975
Smith, F.W., see Mui 97/98 (1987) 999
Smith, Z E., S. Aljishi and S. Wagner, Equilibrium between band tails and dangling bonds in *a*-Si:H 97/98 (1987) 775
Smith, Z E., see Aljishi 97/98 (1987) 1023
Smotlacha, O., see Červinka 97/98 (1987) 183
Snell, A.J., see Choi 97/98 (1987) 1331
Soliman, L.I., see Kenawy 97/98 (1987) 1275
Solomon, I., M.P. Schmidt, C. Senemaud and M. Driss-Khodja, Band-structure and the average-gap model in a-$Si_{1-x}C_x$:H alloys 97/98 (1987) 1091
Sondericker, D., see Yang 97/98 (1987) 851

Sotiropoulos, J. and G. Weiser, Correlation of structure and optical properties of a-$Si_{1-x}C_x$:H alloys 97/98 (1987) 1087
Spear, W., C. Cloude, D. Goldie and P. LeComber, Transport in the electron tail states of amorphous silicon 97/98 (1987) 15
Spear, W.E., see LeComber 97/98 (1987) 1003
Spear, W.E., see Choi 97/98 (1987) 1331
Spence, C.A. and S.R. Elliott, The mechanism of giant photo-contraction in obliquely-deposited thin films of amorphous germanium chalcogenides 97/98 (1987) 1215
Squelard, S., see Theye 97/98 (1987) 1107
Starikov, M.N., see Balagurov 97/98 (1987) 527
Stasiewski, H., see Yang 97/98 (1987) 851
Stefani, F., see Weller 97/98 (1987) 229
Stika, O., see Kočka 97/98 (1987) 819
Stoddart, H.A., Z. Vardeny and J. Tauc, Spectrally resolved transient photomodulated absorption in a-Si:H 97/98 (1987) 125
Stoica, T., see Popescu 97/98 (1987) 1431
Stolka, M. and M.A. Abkowitz, Electronic transport in glassy Si-backbone polymers 97/98 (1987) 1111
Street, R.A., see Marshall 97/98 (1987) 563
Street, R.A., see Kakalios 97/98 (1987) 767
Street, R.A., see Hack 97/98 (1987) 803
Street, R.A., see Stutzmann 97/98 (1987) 1011
Strom, U., J.A. Freitas Jr and S.G. Bishop, Below gap photoinduced paramagnetism in chalcogenide glasses 97/98 (1987) 1183
Stuchlik, J., see Kočka 97/98 (1987) 819
Stuke, J., Problems in the understanding of electronic properties of amorphous silicon 97/98 (1987) 1
Stutzmann, M., Electron spin resonance of shallow defect states in amorphous silicon and germanium 97/98 (1987) 105
Stutzmann, M., C.C. Tsai and R.A. Street, Electronic states in the gap of amorphous silicon–germanium alloys 97/98 (1987) 1011
Su, Z., see Peng 97/98 (1987) 899
Su, Z., J. Liu, S. Peng and Q. Fei, Lateral photovoltaic effect on amorphous silicon junctions 97/98 (1987) 1363
Süptitz, P., see Ressel 97/98 (1987) 1247
Susman, S., see Price 97/98 (1987) 167
Suzuki, M., see Katyal 97/98 (1987) 1195
Symons, J., K. Baert, J. Nijs and R. Mertens, Amorphous and microcrystalline silicon bipolar heterojunction transistors 97/98 (1987) 1315

Tada, T., see Yamaguchi 97/98 (1987) 1199
Tagueña-Martinez, J., see Barrio 97/98 (1987) 499
Taguirdzhanov, M.A., see Bedel'bayeva 97/98 (1987) 1243
Takada, J. and H. Fritzsche, Photo-induced and bias induced metastable states in the transverse conduction of pnpn doping-modulated a-Si:H superlattices 97/98 (1987) 907
Takagi, R., see Nitta 97/98 (1987) 1451
Takahama, T., see Kuwano 97/98 (1987) 289
Takahashi, T., see Nakayama 97/98 (1987) 743
Takenaka, H., see Ogihara 97/98 (1987) 867
Takeuchi, Y., see Matsumura 97/98 (1987) 1299
Talamantes, J., M. Pollak and R. Baron, Moderate-field variable-range hopping transport 97/98 (1987) 555

Tanaka, K., see Okushi 97/98 (1987) 75
Tanaka, K., Physics and chemistry of deposition *(Organizer's summary)* 97/98 (1987) 285
Tanaka, K., Topological phase transitions in amorphous semiconductors *(Invited paper)* 97/98 (1987) 391
Tanaka, K., see Yamasaki 97/98 (1987) 691
Tanaka, K., see Mori 97/98 (1987) 723
Tanaka, K., see Honma 97/98 (1987) 947
Tanaka, K., see Matsuura 97/98 (1987) 963
Tanaka, K., see Matsuda 97/98 (1987) 1367
Tang, W., see Feng 97/98 (1987) 915
Tapiero, M., see Deiss 97/98 (1987) 679
Tarui, H., see Kuwano 97/98 (1987) 289
Tauc, J., see Thomsen 97/98 (1987) 117
Tauc, J., see Stoddart 97/98 (1987) 125
Tauc, J., Band tails in amorphous semiconductors *(Organizer's summary)* 97/98 (1987) 149
Tauc, J., see Grahn 97/98 (1987) 855
Tauc, J., see Zhou 97/98 (1987) 935
Tawada, Y., see Yamagishi 97/98 (1987) 1355
Taylor, P.C., see Ranganathan 97/98 (1987) 707
Taylor, P.C., see Durny 97/98 (1987) 927
Taylor, P.C., see Liu 97/98 (1987) 1123
Terekhov, V.A., see Agafonov 97/98 (1987) 827
Termiane, T., see Naito 97/98 (1987) 1231
Terukov, E.I., see Konkov 97/98 (1987) 1391
Thanailakis, A., see Zdetsis 97/98 (1987) 831
Theye, M.L., see Flank 97/98 (1987) 435
Thèye, M.L., see Chahed 97/98 (1987) 727
Theye, M.L., A. Gheorghiu, D. Udron, C. Senemaud, E. Belin, J. Von Bardeleben, S. Squelard and J. Dupin, Defect states in amorphous InP 97/98 (1987) 1107
Thomas, P., see Götze 97/98 (1987) 217
Thomas, P. and A. Weller, Mode coupling theory for the dephasing and diffusion of excitations 97/98 (1987) 245
Thomas, P., see Djamdji 97/98 (1987) 543
Thomas, P.A. and M. Rosso, Frequency dependence of the ESR in UHV deposited a-Si 97/98 (1987) 755
Thompson, M.J., see Chuang 97/98 (1987) 301
Thompson, M.J., see Marshall 97/98 (1987) 563
Thomsen, C., Z. Vardeny and J. Tauc, Picosecond optical studies of electron and hole thermalization in the band tails of a-Si:H 97/98 (1987) 117
Tichá, H., see Tichý 97/98 (1987) 1227
Tichý, L., see Červinka 97/98 (1987) 183
Tichý, L., see Frumar 97/98 (1987) 1139
Tichý, L., H. Tichá and K. Handlíř, Photoinduced changes of optical properties of amorphous chalcogenide films at ambient air pressure 97/98 (1987) 1227
Tomasi, A., see Dalba 97/98 (1987) 411
Tomiyama, S., see Chuang 97/98 (1987) 301
Tóth, L., D.-S. Kim and H.-S. Pak, Influence of annealing on the DC-electrical transport in undoped amorphous silicon 97/98 (1987) 635
Toyama, T., see Kruangam 97/98 (1987) 293
Toyama, T., see Hattori 97/98 (1987) 1079
Tring, Q.-D., see Kočka 97/98 (1987) 819
Triska, A., see Kočka 97/98 (1987) 819
Tronc, P., Local structure and cohesive energy in Ge_xSe_{1-x} glasses 97/98 (1987) 447
Tsai, C.C., see Boyce 97/98 (1987) 345

Tsai, C.C., see Jackson 97/98 (1987) 891
Tsai, C.C., see Stutzmann 97/98 (1987) 1011
Tsiulyanu, D.I., see Andriesh 97/98 (1987) 1135
Tsu, D.V., see Lucovsky 97/98 (1987) 265
Tsu, D.V. and G. Lucovsky, Properties of the Si–H bond-stretching absorption band in a-Si:H grown by remote plasma enhanced CVD (RPECVD) 97/98 (1987) 839
Tsu, D.V., see Parsons 97/98 (1987) 1375
Tsu, R., Medium range order in amorphous silicon and germanium 97/98 (1987) 163
Tsubusaki, K., see Onuki 97/98 (1987) 1347
Tsuda, S., see Kuwano 97/98 (1987) 289
Tsuda, S., see Hishikawa 97/98 (1987) 399
Tsuge, K., see Yamagishi 97/98 (1987) 1355
Tsukada, T., see Sasano 97/98 (1987) 1295
Tsukude, M., S. Hata, Y. Kohda, S. Miyazaki and M. Hirose, Amorphous silicon superlattice thin film transistors 97/98 (1987) 317
Tsutsumi, Y., S. Sakata, K. Abe, Y. Nitta, H. Okamoto and Y. Hamakawa, Study of gap states in a-SiGe:H alloy system by below-gap modulated photocurrent spectroscopy 97/98 (1987) 1063
Tsvetkova, T., B. Amov, A. Djakov, S. Balabanov and I.H. Wilson, Ion implantation and subsequent annealing influence on some properties of As_3Se_2 films 97/98 (1987) 443
Tuan, H.C., see Chuang 97/98 (1987) 301
Turjanitsa, I.D., see Lisitsa 97/98 (1987) 1159
Turner, G.B., R.J. Schwartz, J.W. Park and J.L. Gray, Recombination in thin film Si:H p-i-n solar cells 97/98 (1987) 1307

Uchida, H., see Kaneko 97/98 (1987) 1359
Uchida, Y., see Ohsawa 97/98 (1987) 91
Uchida, Y., see Asano 97/98 (1987) 971
Uda, T., Computer generation of structural models of hydrogenated amorphous silicon 97/98 (1987) 175
Udron, D., see Flank 97/98 (1987) 435
Udron, D., see Theye 97/98 (1987) 1107
Ueda, M., T. Imura and Y. Osaka, Effect of substrate temperature on the properties of P-doped a-Si:H films prepared at high deposition rate 97/98 (1987) 1387
Ueda, M., see Matsuo 97/98 (1987) 1395

Vaccarezza, C., see Quaresima 97/98 (1987) 979
Vaillant, F., see Valentin 97/98 (1987) 583
Vaillant, F., D. Jousse and J.-C. Bruyère, Respective influence of dangling bonds and band tails as recombination centers in amorphous semiconductors 97/98 (1987) 639
Valentin, F., F. Vaillant and A. Deneuville, Study of localized states in glow discharge a-Si:H from thermally stimulated currents 97/98 (1987) 583
Van Berkel, C., see Powell 97/98 (1987) 321
Van Berkel, C., see Hepburn 97/98 (1987) 903
Van den Heuvel, J.C., see Van Oort 97/98 (1987) 1427
Van der Weg, W.F., see Landweer 97/98 (1987) 711
Van Oort, R.C., M.J. Geerts, J.C. van den Heuvel and J.S. Payson, A PDS study of hydrogenated amorphous silicon films deposited by RF glow-discharge from silane–hydrogen mixtures 97/98 (1987) 1427
Vanderhaghen, R. and C. Longeaud, Experimental determination of hydrogenated amorphous silicon and amorphous silicon–germanium alloy electron transport parameters from time of flight experiment 97/98 (1987) 1059

Vaněček, M., see Bárdoš 97/98 (1987) 281
Vaněček, M., see Kočka 97/98 (1987) 715
Vaněček, M., see Kočka 97/98 (1987) 819
Vardeny, Z. and M. Olszakier, Infrared photomodulation spectroscopy of band tail states in a-Si:H and a-Si:F 97/98 (1987) 109
Vardeny, Z., see Thomsen 97/98 (1987) 117
Vardeny, Z., see Stoddart 97/98 (1987) 125
Vardeny, Z., see Grahn 97/98 (1987) 855
Vardeny, Z., see Zhou 97/98 (1987) 935
Vautier, C., see Misrar 97/98 (1987) 671
Vavilov, V.S., see Kazanskii 97/98 (1987) 787
Velický, B. and A. Pieczonková, Dynamical response of electrons in a disordered solid to a very fast light pulse 97/98 (1987) 455
Velický, B., see Wilke 97/98 (1987) 491
Vieira, M., see Martins 97/98 (1987) 1399
Viner, J., see Durny 97/98 (1987) 927
Vinouze, B., see Le Contellec 97/98 (1987) 297
Viščor, P., Structure and the existence of the first sharp diffraction peak in amorphous germanium prepared in UHV and measured in-situ 97/98 (1987) 179
Vlasov, Yu.G., see Chepeleva 97/98 (1987) 659
Vlček, M. and M. Frumar, Model of photoinduced changes of optical properties in amorphous layers and glasses of Ge–Sb–S, As–S and As–Se systems 97/98 (1987) 1223
Vomvas, A. and H. Fritzsche, The temperature dependence of the photoconductivity of n-type a-Si:H and the effect of Staebler–Wronski defects 97/98 (1987) 823
Von Bardeleben, J., see Theye 97/98 (1987) 1107
Von Hartrott, M., see Draijer 97/98 (1987) 1287
Vuye, G., see Chahed 97/98 (1987) 727

Wagner, H., see Foller 97/98 (1987) 567
Wagner, H., see Beyer 97/98 (1987) 951
Wagner, S., see Fauchet 97/98 (1987) 145
Wagner, S., see Smith 97/98 (1987) 775
Wagner, S., see Conde 97/98 (1987) 939
Wagner, S., see Aljishi 97/98 (1987) 1023
Walloch, F. and L. Ley, Density of gap states in a-Si:H determined by spectrally resolved low temperature IR-photoconductivity 97/98 (1987) 699
Wang, C.A., see Xu 97/98 (1987) 983
Wang, J.Y., see Xu 97/98 (1987) 983
Wang, K., Y. Sawan and M. Silver, Magneto-resistance studies in forward biased hydrogenated amorphous silicon p/i/n devices 97/98 (1987) 631
Wang, S.-L., R.-G. Cheng, M.-W. Qi and P.-X. Cai, IR and H evolution spectrum of a-SiN_x:H with different nitrogen content 97/98 (1987) 1039
Wang, W.C. and H. Fritzsche, Time resolved photoluminescence in a-Si:H: a comparison between single layers and superlattices 97/98 (1987) 919
Watanabe, H., see Zahorowski 97/98 (1987) 843
Watanabe, I. and T. Sekiya, Anomalous electrical conduction in amorphous In_2Se_3 films 97/98 (1987) 667
Watanabe, K., see Hishikawa 97/98 (1987) 399
Watanabe, Y., see Kawazoe 97/98 (1987) 1255
Weaire, D., see Wooten 97/98 (1987) 349
Weber, K., see Djamdji 97/98 (1987) 543
Wegener, D., see Böttger 97/98 (1987) 547

Weil, R., see Deiss 97/98 (1987) 679
Weiser, G., see Pierz 97/98 (1987) 63
Weiser, G., see Sotiropoulos 97/98 (1987) 1087
Weiser, G. and J. Ristein, New insight into recombination and thermalization in As_2Se_3 97/98 (1987) 1131
Weiser, K., see Ritter 97/98 (1987) 571
Weiser, K., see Ritter 97/98 (1987) 619
Weisfield, R., see Chuang 97/98 (1987) 301
Weller, A., see Thomas 97/98 (1987) 245
Weller, H.C., F. Kessler, E. Lotter, C.E. Nebel, S.M. Paasche and G.H. Bauer, Characterization of highly photoconductive amorphous silicon germanium alloys prepared by DC glow discharge 97/98 (1987) 1071
Weller, W., M. Kasner and F. Stefani, Recursion method in the theory of localization – application to two coupled disordered chains, and to electron–phonon interaction in one disordered chain 97/98 (1987) 229
Werner, A. and M. Kunst, Electron and hole kinetics in amorphous silicon 97/98 (1987) 611
Werner, A. and M. Kunst, Influence of light-induced defects on the transient photoconductivity in a-Si:H 97/98 (1987) 791
Wiech, G., see Zahorowski 97/98 (1987) 843
Wilke, S., J. Mašek and B. Velický, Electronic structure of 5d transition metal impurities in amorphous silicon 97/98 (1987) 491
Wilson, I.H., see Tsvetkova 97/98 (1987) 443
Winer, K., see Hirabayashi 97/98 (1987) 87
Winer, K., see Bose 97/98 (1987) 459
Winer, K. and L. Ley, Surface states and the intrinsic valence band tail in a-Si:H 97/98 (1987) 703
Wobst, M., see Neumann 97/98 (1987) 1251
Wong, C.K., G. Lucovsky and J. Bernholc, Intrinsic localized defect states in a-Se associated with dihedral angle distortions 97/98 (1987) 1171
Wooten, F. and D. Weaire, Recent developments with the sillium model 97/98 (1987) 349
Wright, A.C., see Price 97/98 (1987) 167
Wyrsch, N., see Schwarz 97/98 (1987) 759

Xu, Z., see Gu 97/98 (1987) 479
Xu, Z.Y., W. Chen, B.F. Zhao, C.A. Wang, F.Q. Zhang and J.Y. Wang, The effect of the gap DOS in a-Si on the properties of the a-Si/c-Si heterojunction 97/98 (1987) 983

Yadav, P.S., see Agrawal 97/98 (1987) 511
Yamagishi, H., M. Yamaguchi, M. Kondo, Y. Hosokawa, K. Tsuge, T. Nakayama and Y. Tawada, Study of light-induced change in a-SiH solar cells and films by intense light pulse irradiation 97/98 (1987) 1355
Yamaguchi, A., K. Murayama, T. Tada and T. Ninomiya, Temperature dependence of the photoluminescence in a-Si:H and a-As_2S_3 97/98 (1987) 1199
Yamaguchi, M., see Ogihara 97/98 (1987) 867
Yamaguchi, M., H. Ohta, C. Ogihara, H. Yokomichi, K. Morigaki, S. Nonomura and S. Nitta, Gap states and recombination processes in one-dimensionally ordered and disordered a-Si:H/a-$Si_{1-x}N_x$:H multilayer films 97/98 (1987) 931
Yamaguchi, M., see Yamagishi 97/98 (1987) 1355
Yamane, M., see Kawazoe 97/98 (1987) 1255
Yamasaki, S., S. Kuroda, J. Isoya and K. Tanaka, ^{1}H-ENDOR-detected ESR spectra of P- and B-doped a-Si:H 97/98 (1987) 691
Yan, Y., see Chen 97/98 (1987) 341

Yang, C.Y., J.M. Lee, M.A. Paesler and D.E. Sayers, Quantitative measurements of structural changes associated with photo-darkening in a-As_2S_3 films 97/98 (1987) 1119
Yang, C.Y., M.A. Paesler and D.E. Sayers, A new method of measuring optical phonons in amorphous solids: analysis of the mean square relative displacement of EXAFS 97/98 (1987) 1151
Yang, J., T. Glatfelter, R. Ross, R. Mohr, J.P. Fournier and S. Guha, Crucial parameters and device physics of amorphous silicon alloy tandem solar cells 97/98 (1987) 1303
Yang, L., see Abeles 97/98 (1987) 353
Yang, L., B. Abeles, W. Eberhardt, D. Sondericker, H. Stasiewski and Z. Fu, Photoemission study of a-Si:H/a-SiN_x:H interface formation 97/98 (1987) 851
Yang, L., see Sette 97/98 (1987) 895
Yang, L. and B. Abeles, Quantum shift of the optical absorption edge in ultra thin amorphous hydrogenated germanium layers 97/98 (1987) 1155
Yang, L.H., see Nichols 97/98 (1987) 495
Yasuda, A., see Nitta 97/98 (1987) 1451
Yokomichi, H. and K. Morigaki, Observation of different types of dangling bonds and their photo-creation in a-Si:H, as elucidated by ENDOR measurements 97/98 (1987) 67
Yokomichi, H., see Yamaguchi 97/98 (1987) 931
Yonezawa, F., S. Nosé and S. Sakamoto, Computer simulations of preparation and annealing of amorphous solids *(Special presentation)* 97/98 (1987) 373
Yoo, B.-S., see Choi 97/98 (1987) 911
Yoshida, M. and K. Morigaki, Triplet exciton recombination in silicon-based amorphous semiconductors 97/98 (1987) 579
Yoshida, M., see Han 97/98 (1987) 651
Yue, J., see Matsumura 97/98 (1987) 1299

Zahorowski, W., R. Knop, H. Watanabe and G. Wiech, X-ray spectroscopic study of the electronic structure of amorphous SiN_x:H ($0.04 \leqslant x \leqslant 0.44$) 97/98 (1987) 843
Zakery, A., see Ewen 97/98 (1987) 1127
Zayed, H.A., see Kenawy 97/98 (1987) 1275
Zdanowicz, L. and B. Jarząbek, Optical properties of amorphous cadmium arsenide 97/98 (1987) 1203
Zdetsis, A.D., A theoretical self-consistent model for electronic and optical properties of hydrogenated amorphous alloys 97/98 (1987) 515
Zdetsis, A.D., D. Girginoudi, G. Kiriakidis, Z. Hatzopoulos, A. Thanailakis and A. Christou, Physical properties of amorphous silicon alloy films: comparison with electronic structure calculations 97/98 (1987) 831
Zeindl, H.P., see Petrova-Koch 97/98 (1987) 807
Zeldov, E., see Ritter 97/98 (1987) 571
Zeldov, E., see Ritter 97/98 (1987) 619
Zemek, J., see Pajasová 97/98 (1987) 451
Zentai, Gy., see Füstöss-Wégner 97/98 (1987) 1327
Zhang, F.O., Y.F. Zhang, Z. Liu and G.H. Chen, A study of electroluminescence in a-$Si_{1-x}C_x$:H and a-Si:H devices with various structures 97/98 (1987) 1311
Zhang, F.Q., see Xu 97/98 (1987) 983
Zhang, Y.F., see Zhang 97/98 (1987) 1311
Zhang, Z.Y., R.G. Cheng and H. Fritzsche, Electrical properties of a-Si:H/a-SiC_x:H multilayers 97/98 (1987) 923
Zhao, B.F., see Xu 97/98 (1987) 983
Zherzdev, A.V., see Kosarev 97/98 (1987) 615

Zhou, T.X., Z. Vardeny and J. Tauc, Photomodulation spectroscopy of states in the gap in phosphorus doped a-Si:H and a-Si:H/a-SiN_x:H multilayer structures 97/98 (1987) 935
Zielinger, J.P., see Deiss 97/98 (1987) 679
Zmeškal, O., see Schauer 97/98 (1987) 747
Zmeškal, O., see Schauer 97/98 (1987) 811
Zmeškal, O., see Salyk 97/98 (1987) 1435
Zubík, K., see Salyk 97/98 (1987) 1435
Zvyagin, I.P., Dangling bond as a variable-*U* defect in a-Si:H 97/98 (1987) 83

Journal of Non-Crystalline Solids 97&98 (1987) 1503–1524
North-Holland, Amsterdam

SUBJECT INDEX

Absorption
Electronic Structure, Optical Properties 97/98 (1987) 63
Interfaces, Optical Properties 97/98 (1987) 975
Optical Properties 97/98 (1987) 935
Optical Properties, Superlattices 97/98 (1987) 927
Optical Properties, Theory 97/98 (1987) 527
Photoinduced Effects, Stäbler–Wronski Effect 97/98 (1987) 787

Acoustic Properties
Phonons, Raman Spectra 97/98 (1987) 859

Amorphous Solids
Electrical Properties 97/98 (1987) 1
Semiconductors, Electronic Structure 97/98 (1987) 95

Applications
Computer Simulation, Electronic Conductivity, Transport Properties – Solids 97/98 (1987) 1299
Crystallization, Surface Properties 97/98 (1987) 1315
Diffusion, Fabrication 97/98 (1987) 1295
Silicon, Thin Films 97/98 (1987) 297
Silicon, Transistors 97/98 (1987) 301
Silicon, Transistors 97/98 (1987) 313
Silicon, Transistors 97/98 (1987) 1291
Superlattices, Transport Properties – Solids 97/98 (1987) 317
Surface Properties, Transport Properties – Solids 97/98 (1987) 1359
Transport Properties – Solids 97/98 (1987) 305

Auger Electron Spectroscopy
Secondary Ion Mass Spectroscopy, Silicon Alloys 97/98 (1987) 951

Bonding
Medium-Range Order, Structure 97/98 (1987) 155
Silicon 97/98 (1987) 1043

Calorimetry
Photoconductivity 97/98 (1987) 779

Capacitance Methods
Electrical Properties, Silicon, Stability 97/98 (1987) 803
Electrical Properties, Transport Properties – Solids 97/98 (1987) 723

Carbon
Deposition Techniques, Polymers 97/98 (1987) 1451
Electronic Structure, Phase Separation 97/98 (1987) 1095
Electronic Structure, Structure 97/98 (1987) 199

Catalysis
Deposition Techniques 97/98 (1987) 1379

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Chalcogenides
Coatings, Optical Properties 97/98 (1987) 1191
Computer Simulation, Structure 97/98 (1987) 383
Defects, Nuclear Magnetic Resonance 97/98 (1987) 1175
Defects, Photoconductivity 97/98 (1987) 663
Defects, Photoconductivity 97/98 (1987) 687
Defects, Trapping 97/98 (1987) 1171
Diffusion, Radiation Effects 97/98 (1987) 1247
Electrical Properties 97/98 (1987) 1163
Electrical Properties, High Field Effects 97/98 (1987) 1131
Electrical Properties, Photoconductivity 97/98 (1987) 987
Electron Spin Resonance, Gap States 97/98 (1987) 1183
Electron Spin Resonance, Impurity Conduction, Mössbauer Effect 97/98 (1987) 659
Electron Spin Resonance, Liquids 97/98 (1987) 1255
Electron Spin Resonance, Radiation Effects 97/98 (1987) 1179
Electronic Conductivity, Thermoelectric Power 97/98 (1987) 1139
Electronic Structure, Optical Properties 97/98 (1987) 1147
EXAFS, Radiation Effects 97/98 (1987) 1119
EXAFS, X-ray Diffraction 97/98 (1987) 411
Fermi Level 97/98 (1987) 1135
Germanates 97/98 (1987) 427
Impurities, Radiation Effects 97/98 (1987) 1243
Infra-red Absorption 97/98 (1987) 1187
Ion Implantation, Surface Properties 97/98 (1987) 443
Kinetics, Lasers 97/98 (1987) 1235
Liquids, Structure 97/98 (1987) 1251
Liquids, Structure 97/98 (1987) 1271
Neutron Diffraction, Raman Spectra 97/98 (1987) 167
Non-oxide Glasses, Optical Properties 97/98 (1987) 1279
Optical Properties 97/98 (1987) 1123
Optical Properties 97/98 (1987) 1127
Optical Properties 97/98 (1987) 1159
Optical Properties 97/98 (1987) 1227
Optical Properties, Photoinduced Effects 97/98 (1987) 1207
Optical Properties, Silicon 97/98 (1987) 1199
Optical Properties, Thin Films 97/98 (1987) 1219
Photo Voltage 97/98 (1987) 47
Photoconductivity 97/98 (1987) 675
Photoconductivity, Photoinduced Effects 97/98 (1987) 1195
Photoconductivity, Transport Properties – Solids 97/98 (1987) 667
Photoinduced Effects 97/98 (1987) 1223
Radiation Effects, Small Angle X-ray Scattering 97/98 (1987) 1215
Radiation Effects, Thin Films 97/98 (1987) 1239
Structure 97/98 (1987) 379
Structure 97/98 (1987) 439
Structure 97/98 (1987) 447
Structure 97/98 (1987) 1275
Transport Properties – Liquids, Transport Properties – Solids 97/98 (1987) 1231

Coatings
Chalcogenides, Optical Properties 97/98 (1987) 1191

Computer Simulation
Applications, Electronic Conductivity, Transport Properties – Solids 97/98 (1987) 1299

Chalcogenides, Structure 97/98 (1987) 383
Density of States, Electronic Structure 97/98 (1987) 241
Density of States, Electronic Structure 97/98 (1987) 483
Electrical Properties, Heterojunctions, Silicon 97/98 (1987) 983
Electronic Conductivity, Impurity Conduction 97/98 (1987) 31
Electronic Structure, Impurity Conduction 97/98 (1987) 233
Experimental Techniques, Photoconductivity 97/98 (1987) 607
Glass Formation, Glass Transition 97/98 (1987) 373
Liquids, Structure 97/98 (1987) 187
Phase Transition, Transport Properties – Solids 97/98 (1987) 221
Photo-emission 97/98 (1987) 133
Silica, Surface Properties 97/98 (1987) 195
Silicon, Structure 97/98 (1987) 175
Solar Cells 97/98 (1987) 1307
Tetrahedral Materials 97/98 (1987) 349

Crystallization
Applications, Surface Properties 97/98 (1987) 1315
Liquids, Structure 97/98 (1987) 1259
Phase Separation, Structure 97/98 (1987) 55
Sputtering, Thermodynamics 97/98 (1987) 947

Dangling Bonds
Defects, Electronic Conductivity, Electronic Structure 97/98 (1987) 83
Density of States, Silicon 97/98 (1987) 715
Electron Microscopy, Gap States, Sintering 97/98 (1987) 79
Electron Spin Resonance, Glow Discharge, Sputtering 97/98 (1987) 67
Electronic Conductivity, Transport Properties – Solids 97/98 (1987) 799
Electronic Structure, Transistors 97/98 (1987) 1339
Photoconductivity, Recombination 97/98 (1987) 639
Silicon Nitride, Stability, Transistors 97/98 (1987) 321

Defects
Chalcogenides, Nuclear Magnetic Resonance 97/98 (1987) 1175
Chalcogenides, Photoconductivity 97/98 (1987) 663
Chalcogenides, Photoconductivity 97/98 (1987) 687
Chalcogenides, Trapping 97/98 (1987) 1171
Dangling Bonds, Electronic Conductivity, Electronic Structure 97/98 (1987) 83
Electrical Properties, Electron Spin Resonance, Superlattices 97/98 (1987) 875
Electron Spin Resonance, Silicon Alloys 97/98 (1987) 1015
Electronic Structure, Semiconductors 97/98 (1987) 415
Optical Properties, XPS 97/98 (1987) 1107
Silicon 97/98 (1987) 463
Theory, Thermodynamics 97/98 (1987) 467

Density of States
Computer Simulation, Electronic Structure 97/98 (1987) 241
Computer Simulation, Electronic Structure 97/98 (1987) 483
Dangling Bonds, Silicon 97/98 (1987) 715
Deposition Techniques, Silicon 97/98 (1987) 1391
Electrical Properties, Electronic Structure, Ion Implantation 97/98 (1987) 763
Electron Spin Resonance, Radiation Effects 97/98 (1987) 795
Electronic Structure, Silicon 97/98 (1987) 747
Electronic Structure, Silicon Alloys 97/98 (1987) 507

Optical Properties, Silicon Alloys, Theory 97/98 (1987) 515
Optical Properties, Superlattices 97/98 (1987) 751
Silicon, Silicon Alloys 97/98 (1987) 1059
Silicon, Stäbler–Wronski Effect 97/98 (1987) 811
Silicon, Theory 97/98 (1987) 499
Silicon, Transport Properties – Solids 97/98 (1987) 563
Silicon Alloys 97/98 (1987) 1455
Silicon Alloys, Thermoelectric Power 97/98 (1987) 511
Silicon Nitride, X-ray Emission 97/98 (1987) 827
Tails 97/98 (1987) 101

Deposition Techniques
Carbon, Polymers 97/98 (1987) 1451
Catalysis 97/98 (1987) 1379
Density of States, Silicon 97/98 (1987) 1391
Electron Spin Resonance 97/98 (1987) 755
Electronic Structure, Silicon 97/98 (1987) 1435
Ellipsometry, Nucleation 97/98 (1987) 269
Porosity, Silicon 97/98 (1987) 1431
Silicon, Thin Films 97/98 (1987) 265
Surface Properties 97/98 (1987) 261

Dielectric Properties
Electronic Structure, XPS 97/98 (1987) 431
Liquid Semiconductors, Silicon 97/98 (1987) 1267

Diffusion
Applications, Fabrication 97/98 (1987) 1295
Chalcogenides, Radiation Effects 97/98 (1987) 1247
Electrical Properties, Electronic Conductivity 97/98 (1987) 767
Electronic Conductivity, Phase Transition, Transport Properties – Solids 97/98 (1987) 759
Experimental Techniques, Fabrication 97/98 (1987) 1423
Hydrogen Effects, Infra-red Absorption 97/98 (1987) 807
Impurities, Silicon 97/98 (1987) 353
Impurity Conduction, Optical Properties 97/98 (1987) 1415
Theory 97/98 (1987) 245

Diodes
III–V semiconductors, Optical Properties, Photoconductivity 97/98 (1987) 1347
Photoconductivity, Silicon, Transport Properties – Solids 97/98 (1987) 1323

Electrical Properties
Amorphous Solids 97/98 (1987) 1
Capacitance Methods, Silicon, Stability 97/98 (1987) 803
Capacitance Methods, Transport Properties – Solids 97/98 (1987) 723
Chalcogenides 97/98 (1987) 1163
Chalcogenides, High Field Effects 97/98 (1987) 1131
Chalcogenides, Photoconductivity 97/98 (1987) 987
Computer Simulation, Heterojunctions, Silicon 97/98 (1987) 983
Defects, Electron Spin Resonance, Superlattices 97/98 (1987) 875
Density of States, Electronic Structure, Ion Implantation 97/98 (1987) 763
Diffusion, Electronic Conductivity 97/98 (1987) 767
Electronic Conductivity 97/98 (1987) 643
Electronic Conductivity, Magnetic Properties 97/98 (1987) 249

Electronic Structure, Optical Properties 97/98 (1987) 71
Electronic Structure, Photoconductivity 97/98 (1987) 611
Experimental Techniques, Photo-emission 97/98 (1987) 75
Gap States, Metastability 97/98 (1987) 815
Kinetics, Optical Properties 97/98 (1987) 137
Optical Properties, Silicon 97/98 (1987) 1375
Photo-emission, Relaxation 97/98 (1987) 595
Photoconductivity, Thin Films, Transport Properties – Solids 97/98 (1987) 1055
Photoinduced Effects, X-ray Diffraction 97/98 (1987) 679
Silicon 97/98 (1987) 695
Silicon, Time-Resolved Spectroscopy 97/98 (1987) 121
Silicon Alloys 97/98 (1987) 419
Silicon Alloys, Structure 97/98 (1987) 1027
Silicon Nitride 97/98 (1987) 1003
Transport Properties – Solids 97/98 (1987) 635

Electron Diffraction
Superlattices 97/98 (1987) 341

Electron Microscopy
Dangling Bonds, Gap States, Sintering 97/98 (1987) 79
Interfaces 97/98 (1987) 959

Electron Spin Resonance
Chalcogenides, Gap States 97/98 (1987) 1183
Chalcogenides, Impurity Conduction, Mössbauer Effect 97/98 (1987) 659
Chalcogenides, Liquids 97/98 (1987) 1255
Chalcogenides, Radiation Effects 97/98 (1987) 1179
Dangling Bonds, Glow Discharge, Sputtering 97/98 (1987) 67
Defects, Electrical Properties, Superlattices 97/98 (1987) 875
Defects, Silicon Alloys 97/98 (1987) 1015
Density of States, Radiation Effects 97/98 (1987) 795
Deposition Techniques 97/98 (1987) 755
Electronic Structure 97/98 (1987) 105
Electronic Structure, Infra-red Absorption, Optical Properties, Sputtering 97/98 (1987) 831
Electronic Structure, Thin Films 97/98 (1987) 1083
Gap States, Silicon Alloys 97/98 (1987) 1011
Luminescence, Superlattices 97/98 (1987) 867
Optical Properties 97/98 (1987) 1047
Raman Spectra, Silicon 97/98 (1987) 91
Structure 97/98 (1987) 691

Electronic Conductivity
Applications, Computer Simulation, Transport Properties – Solids 97/98 (1987) 1299
Chalcogenides, Thermoelectric Power 97/98 (1987) 1139
Computer Simulation, Impurity Conduction 97/98 (1987) 31
Dangling Bonds, Defects, Electronic Structure 97/98 (1987) 83
Dangling Bonds, Transport Properties – Solids 97/98 (1987) 799
Diffusion, Electrical Properties 97/98 (1987) 767
Diffusion, Phase Transition, Transport Properties – Solids 97/98 (1987) 759
Electrical Properties 97/98 (1987) 643
Electrical Properties, Magnetic Properties 97/98 (1987) 249
Field Effect 97/98 (1987) 543
High Field Effects, Impurity Conduction 97/98 (1987) 555

III–V semiconductors, Metal–Insulator Transition 97/98 (1987) 1459
Impurity Conduction, Magnetic Properties 97/98 (1987) 683
Interfaces 97/98 (1987) 923
Metal–Insulator Transition 97/98 (1987) 225
Photoconductivity 97/98 (1987) 627
Photoconductivity 97/98 (1987) 911
Photoconductivity, Photoinduced Effects 97/98 (1987) 791
Polymers 97/98 (1987) 1111
Silicon Alloys, Sputtering 97/98 (1987) 955
Theory, Transport Properties – Solids 97/98 (1987) 229
Theory, Transport Properties – Solids 97/98 (1987) 475
Thermoelectric Power 97/98 (1987) 539
Thin Films, Transport Properties – Solids 97/98 (1987) 671
Transient Effects 97/98 (1987) 129

Electronic Structure
Absorption, Optical Properties 97/98 (1987) 63
Amorphous Solids, Semiconductors 97/98 (1987) 95
Carbon, Phase Separation 97/98 (1987) 1095
Carbon, Structure 97/98 (1987) 199
Chalcogenides, Optical Properties 97/98 (1987) 1147
Computer Simulation, Density of States 97/98 (1987) 241
Computer Simulation, Density of States 97/98 (1987) 483
Computer Simulation, Impurity Conduction 97/98 (1987) 233
Dangling Bonds, Defects, Electronic Conductivity 97/98 (1987) 83
Dangling Bonds, Transistors 97/98 (1987) 1339
Defects, Semiconductors 97/98 (1987) 415
Density of States, Electrical Properties, Ion Implantation 97/98 (1987) 763
Density of States, Silicon 97/98 (1987) 747
Density of States, Silicon Alloys 97/98 (1987) 507
Deposition Techniques, Silicon 97/98 (1987) 1435
Dielectric Properties, XPS 97/98 (1987) 431
Electrical Properties, Optical Properties 97/98 (1987) 71
Electrical Properties, Photoconductivity 97/98 (1987) 611
Electron Spin Resonance 97/98 (1987) 105
Electron Spin Resonance, Infra-red Absorption, Optical Properties, Sputtering 97/98 (1987) 831
Electron Spin Resonance, Thin Films 97/98 (1987) 1083
Experimental Techniques 97/98 (1987) 743
Glass Transition 97/98 (1987) 775
Heterojunctions, Photo-emission 97/98 (1987) 863
Impurities, Silicon 97/98 (1987) 495
Impurities, Theory 97/98 (1987) 491
Impurity Conduction, Theory 97/98 (1987) 237
Interfaces, Photo-emission 97/98 (1987) 899
Optical Properties, Photoconductivity 97/98 (1987) 699
Photo-emission 97/98 (1987) 1007
Photo-emission, Silicon Alloys 97/98 (1987) 407
Photo-emission, Surface Properties 97/98 (1987) 1411
Photoconductivity 97/98 (1987) 603
Silicon 97/98 (1987) 583
Silicon, Theory 97/98 (1987) 459
Silicon, Transport Properties – Solids 97/98 (1987) 15
Silicon Alloys, Transient Effects 97/98 (1987) 1023
Silicon Alloys, X-ray Emission 97/98 (1987) 843

Structure, Thin Films 97/98 (1987) 179
Transport Properties – Solids 97/98 (1987) 655

Ellipsometry
Deposition Techniques, Nucleation 97/98 (1987) 269
Growth Kinetics, Thin Films 97/98 (1987) 1403

EXAFS
Chalcogenides, Radiation Effects 97/98 (1987) 1119
Chalcogenides, X-ray Diffraction 97/98 (1987) 411
Germanium 97/98 (1987) 519
Optical Properties 97/98 (1987) 1103
Phonons 97/98 (1987) 1151
Silicon Alloys 97/98 (1987) 365
Structure 97/98 (1987) 403
Structure, Tetrahedral Materials 97/98 (1987) 435

Experimental Techniques
Computer Simulation, Photoconductivity 97/98 (1987) 607
Diffusion, Fabrication 97/98 (1987) 1423
Electrical Properties, Photo-emission 97/98 (1987) 75
Electronic Structure 97/98 (1987) 743
Glow Discharge, Transistors 97/98 (1987) 735

Fabrication
Applications, Diffusion 97/98 (1987) 1295
Diffusion, Experimental Techniques 97/98 (1987) 1423
Glow Discharge, Optical Properties 97/98 (1987) 1427
Microwave, Thin Films 97/98 (1987) 277
Silicon, Thin Films 97/98 (1987) 281

Fermi Level
Chalcogenides 97/98 (1987) 1135

Field Effect
Electronic Conductivity 97/98 (1987) 543

Fluorides
Phase Separation 97/98 (1987) 257

Gap States
Chalcogenides, Electron Spin Resonance 97/98 (1987) 1183
Dangling Bonds, Electron Microscopy, Sintering 97/98 (1987) 79
Electrical Properties, Metastability 97/98 (1987) 815
Electron Spin Resonance, Silicon Alloys 97/98 (1987) 1011
Photoconductivity, Stress Relaxation 97/98 (1987) 819
Photoinduced Effects 97/98 (1987) 1063

Germanates
Chalcogenides 97/98 (1987) 427
Pressure Effects 97/98 (1987) 1115

Germanium
EXAFS 97/98 (1987) 519
Optical Properties, Thin Films 97/98 (1987) 1155

Photoinduced Effects, Silicon 97/98 (1987) 1067
Raman Spectra, Silicon 97/98 (1987) 163

Glass Formation
Computer Simulation, Glass Transition 97/98 (1987) 373

Glass Transition
Computer Simulation, Glass Formation 97/98 (1987) 373
Electronic Structure 97/98 (1987) 775
Memory Behaviour, Non-oxide Glasses, Phase Transition 97/98 (1987) 1351

Glow Discharge
Dangling Bonds, Electron Spin Resonance, Sputtering 97/98 (1987) 67
Experimental Techniques, Transistors 97/98 (1987) 735
Fabrication, Optical Properties 97/98 (1987) 1427
Multilayers, Structure 97/98 (1987) 1439
Photoconductivity, Silicon Alloys 97/98 (1987) 1447
Photoconductivity, Silicon Alloys, Transport Properties – Solids 97/98 (1987) 1071
Silicon 97/98 (1987) 623

Growth Kinetics
Ellipsometry, Thin Films 97/98 (1987) 1403
Silicon, Transport Properties – Solids 97/98 (1987) 1399

Heterojunctions
Computer Simulation, Electrical Properties, Silicon 97/98 (1987) 983
Electronic Structure, Photo-emission 97/98 (1987) 863
Optical Properties 97/98 (1987) 971
Photo Voltage, Silicon 97/98 (1987) 1363
Silicon Alloys, Structure 97/98 (1987) 895
Silicon Alloys, Transport Properties – Solids 97/98 (1987) 1319

High Field Effects
Chalcogenides, Electrical Properties 97/98 (1987) 1131
Electronic Conductivity, Impurity Conduction 97/98 (1987) 555
Hopping, Theory 97/98 (1987) 547
Transport Properties – Solids 97/98 (1987) 559

Hopping
High Field Effects, Theory 97/98 (1987) 547
Silicates, Transport Properties – Solids 97/98 (1987) 523

Hydrogen Effects
Diffusion, Infra-red Absorption 97/98 (1987) 807
Silicon, Structure 97/98 (1987) 1395

Hydrogenation
Photo-emission, Surface Properties 97/98 (1987) 1407

III–V semiconductors
Diodes, Optical Properties, Photoconductivity 97/98 (1987) 1347
Electronic Conductivity, Metal–Insulator Transition 97/98 (1987) 1459

Image Sensors
Silicon, Transistors 97/98 (1987) 1343

Impurities
Chalcogenides, Radiation Effects 97/98 (1987) 1243
Diffusion, Silicon 97/98 (1987) 353
Electronic Structure, Silicon 97/98 (1987) 495
Electronic Structure, Theory 97/98 (1987) 491
Liquid Semiconductors 97/98 (1987) 1287
Nuclear Magnetic Resonance, Silicon 97/98 (1987) 357
Thin Films 97/98 (1987) 1419

Impurity Conduction
Chalcogenides, Electron Spin Resonance, Mössbauer Effect 97/98 (1987) 659
Computer Simulation, Electronic Conductivity 97/98 (1987) 31
Computer Simulation, Electronic Structure 97/98 (1987) 233
Diffusion, Optical Properties 97/98 (1987) 1415
Electronic Conductivity, High Field Effects 97/98 (1987) 555
Electronic Conductivity, Magnetic Properties 97/98 (1987) 683
Electronic Structure, Theory 97/98 (1987) 237
Localization 97/98 (1987) 213

Infra-red Absorption
Chalcogenides 97/98 (1987) 1187
Diffusion, Hydrogen Effects 97/98 (1987) 807
Electron Spin Resonance, Electronic Structure, Optical Properties, Sputtering 97/98 (1987) 831
Lattice Dynamics, Silicon 97/98 (1987) 839
Metallic Glasses 97/98 (1987) 835
Optical Properties, Photoconductivity 97/98 (1987) 1075
Optical Properties, Relaxation 97/98 (1987) 109
Optical Properties, Superlattices 97/98 (1987) 943
Silica 97/98 (1987) 1051
Silicon, Structure 97/98 (1987) 1387

Injection of Carriers
Luminescence, Silicon 97/98 (1987) 1311
Optical Properties, Silicon Alloys 97/98 (1987) 293

Interfaces
Absorption, Optical Properties 97/98 (1987) 975
Electron Microscopy 97/98 (1987) 959
Electronic Conductivity 97/98 (1987) 923
Electronic Structure, Photo-emission 97/98 (1987) 899
Optical Properties, Recombination 97/98 (1987) 931
Photo-emission 97/98 (1987) 979
Photo-emission, Silicon 97/98 (1987) 851
Photoconductivity, Thin Films 97/98 (1987) 967
Silicon Nitride, Trapping 97/98 (1987) 891

Ion Implantation
Chalcogenides, Surface Properties 97/98 (1987) 443
Density of States, Electrical Properties, Electronic Structure 97/98 (1987) 763
Phosphates, Thin Films 97/98 (1987) 273

Kinetics
Chalcogenides, Lasers 97/98 (1987) 1235
Electrical Properties, Optical Properties 97/98 (1987) 137

Lasers, Thin Films 97/98 (1987) 1443
Optical Properties 97/98 (1987) 1383
Raman Spectra, Theory 97/98 (1987) 487
Silicon 97/98 (1987) 783
Thin Films 97/98 (1987) 1367

Lasers
Chalcogenides, Kinetics 97/98 (1987) 1235
Kinetics, Thin Films 97/98 (1987) 1443

Lattice Dynamics
Infra-red Absorption, Silicon 97/98 (1987) 839

Liquid Semiconductors
Dielectric Properties, Silicon 97/98 (1987) 1267
Impurities 97/98 (1987) 1287
Neutron Diffraction, Structure 97/98 (1987) 1263
Neutron Diffraction, Structure 97/98 (1987) 1283

Liquids
Chalcogenides, Electron Spin Resonance 97/98 (1987) 1255
Chalcogenides, Structure 97/98 (1987) 1251
Chalcogenides, Structure 97/98 (1987) 1271
Computer Simulation, Structure 97/98 (1987) 187
Crystallization, Structure 97/98 (1987) 1259

Localization
Impurity Conduction 97/98 (1987) 213
Mobility Edge, Theory 97/98 (1987) 531

Luminescence
Electron Spin Resonance, Superlattices 97/98 (1987) 867
Injection of Carriers, Silicon 97/98 (1987) 1311
Optical Properties, Recombination 97/98 (1987) 915
Optical Properties, Superlattices 97/98 (1987) 919
Silicon Alloys, Superlattices 97/98 (1987) 883

Magnetic Properties
Electrical Properties, Electronic Conductivity 97/98 (1987) 249
Electronic Conductivity, Impurity Conduction 97/98 (1987) 683
Silicon 97/98 (1987) 631

Medium-Range Order
Bonding, Structure 97/98 (1987) 155
Short-Range Order, Structure 97/98 (1987) 159

Memory Behaviour
Glass Transition, Non-oxide Glasses, Phase Transition 97/98 (1987) 1351
Silicon, Switching 97/98 (1987) 1331

Metal–Insulator Transition
Electronic Conductivity 97/98 (1987) 225
Electronic Conductivity, III–V semiconductors 97/98 (1987) 1459
Theory 97/98 (1987) 217

Metallic Glasses
Infra-red Absorption 97/98 (1987) 835

Metastability
Electrical Properties, Gap States 97/98 (1987) 815

Microwave
Fabrication, Thin Films 97/98 (1987) 277

Mobility Edge
Localization, Theory 97/98 (1987) 531

Mössbauer Effect
Chalcogenides, Electron Spin Resonance, Impurity Conduction 97/98 (1987) 659
Silicon, Structure 97/98 (1987) 361

Multilayers
Glow Discharge, Structure 97/98 (1987) 1439
Silicon, Silicon Nitride, Superlattices 97/98 (1987) 23

Neutron Diffraction
Chalcogenides, Raman Spectra 97/98 (1987) 167
Liquid Semiconductors, Structure 97/98 (1987) 1263
Liquid Semiconductors, Structure 97/98 (1987) 1283
Silicon, Structure 97/98 (1987) 337
Structure 97/98 (1987) 329

Non-oxide Glasses
Chalcogenides, Optical Properties 97/98 (1987) 1279
Glass Transition, Memory Behaviour, Phase Transition 97/98 (1987) 1351

Nuclear Magnetic Resonance
Chalcogenides, Defects 97/98 (1987) 1175
Impurities, Silicon 97/98 (1987) 357
Structure 97/98 (1987) 345

Nucleation
Deposition Techniques, Ellipsometry 97/98 (1987) 269

Optical Properties
Absorption 97/98 (1987) 935
Absorption, Electronic Structure 97/98 (1987) 63
Absorption, Interfaces 97/98 (1987) 975
Absorption, Superlattices 97/98 (1987) 927
Absorption, Theory 97/98 (1987) 527
Chalcogenides 97/98 (1987) 1123
Chalcogenides 97/98 (1987) 1127
Chalcogenides 97/98 (1987) 1159
Chalcogenides 97/98 (1987) 1227
Chalcogenides, Coatings 97/98 (1987) 1191
Chalcogenides, Electronic Structure 97/98 (1987) 1147
Chalcogenides, Non-oxide Glasses 97/98 (1987) 1279
Chalcogenides, Photoinduced Effects 97/98 (1987) 1207
Chalcogenides, Silicon 97/98 (1987) 1199

Chalcogenides, Thin Films 97/98 (1987) 1219
Defects, XPS 97/98 (1987) 1107
Density of States, Silicon Alloys, Theory 97/98 (1987) 515
Density of States, Superlattices 97/98 (1987) 751
Diffusion, Impurity Conduction 97/98 (1987) 1415
Diodes, III–V semiconductors, Photoconductivity 97/98 (1987) 1347
Electrical Properties, Electronic Structure 97/98 (1987) 71
Electrical Properties, Kinetics 97/98 (1987) 137
Electrical Properties, Silicon 97/98 (1987) 1375
Electron Spin Resonance 97/98 (1987) 1047
Electron Spin Resonance, Electronic Structure, Infra-red Absorption, Sputtering 97/98 (1987) 831
Electronic Structure, Photoconductivity 97/98 (1987) 699
EXAFS 97/98 (1987) 1103
Fabrication, Glow Discharge 97/98 (1987) 1427
Germanium, Thin Films 97/98 (1987) 1155
Heterojunctions 97/98 (1987) 971
Infra-red Absorption, Photoconductivity 97/98 (1987) 1075
Infra-red Absorption, Relaxation 97/98 (1987) 109
Infra-red Absorption, Superlattices 97/98 (1987) 943
Injection of Carriers, Silicon Alloys 97/98 (1987) 293
Interfaces, Recombination 97/98 (1987) 931
Kinetics 97/98 (1987) 1383
Luminescence, Recombination 97/98 (1987) 915
Luminescence, Superlattices 97/98 (1987) 919
Photo-emission, Silicon Alloys 97/98 (1987) 451
Photoconductivity, Silicon 97/98 (1987) 727
Photoinduced Effects 97/98 (1987) 615
Photoinduced Effects, Silicon 97/98 (1987) 651
Raman Spectra, Structure 97/98 (1987) 387
Relaxation 97/98 (1987) 141
Silicon, X-ray Diffraction 97/98 (1987) 191
Silicon Alloys 97/98 (1987) 991
Silicon Alloys, Structure 97/98 (1987) 1087
Silicon Alloys, Thin Films 97/98 (1987) 999
Silicon Alloys, X-ray Emission 97/98 (1987) 1091
Transport Properties – Solids 97/98 (1987) 1079

Oxides
Phase Separation, Structure 97/98 (1987) 423

Phase Separation
Carbon, Electronic Structure 97/98 (1987) 1095
Crystallization, Structure 97/98 (1987) 55
Fluorides 97/98 (1987) 257
Oxides, Structure 97/98 (1987) 423

Phase Transition
Computer Simulation, Transport Properties – Solids 97/98 (1987) 221
Diffusion, Electronic Conductivity, Transport Properties – Solids 97/98 (1987) 759
Glass Transition, Memory Behaviour, Non-oxide Glasses 97/98 (1987) 1351
Pressure Effects, Structure 97/98 (1987) 391

Phonons
Acoustic Properties, Raman Spectra 97/98 (1987) 859
EXAFS 97/98 (1987) 1151

Phosphates
Ion Implantation, Thin Films 97/98 (1987) 273

Photo-emission
Computer Simulation 97/98 (1987) 133
Electrical Properties, Experimental Techniques 97/98 (1987) 75
Electrical Properties, Relaxation 97/98 (1987) 595
Electronic Structure 97/98 (1987) 1007
Electronic Structure, Heterojunctions 97/98 (1987) 863
Electronic Structure, Interfaces 97/98 (1987) 899
Electronic Structure, Silicon Alloys 97/98 (1987) 407
Electronic Structure, Surface Properties 97/98 (1987) 1411
Hydrogenation, Surface Properties 97/98 (1987) 1407
Interfaces 97/98 (1987) 979
Interfaces, Silicon 97/98 (1987) 851
Optical Properties, Silicon Alloys 97/98 (1987) 451
Silicon 97/98 (1987) 647
Silicon 97/98 (1987) 707
Silicon, Surface Properties 97/98 (1987) 87
Silicon, Surface Properties 97/98 (1987) 847
Structure 97/98 (1987) 1211
Superlattices, Transport Properties – Solids 97/98 (1987) 907
Surface Properties 97/98 (1987) 703
Transport Properties – Solids 97/98 (1987) 855

Photo Voltage
Chalcogenides 97/98 (1987) 47
Heterojunctions, Silicon 97/98 (1987) 1363
Silicon, Surface Properties 97/98 (1987) 567

Photoconductivity
Calorimetry 97/98 (1987) 779
Chalcogenides 97/98 (1987) 675
Chalcogenides, Defects 97/98 (1987) 663
Chalcogenides, Defects 97/98 (1987) 687
Chalcogenides, Electrical Properties 97/98 (1987) 987
Chalcogenides, Photoinduced Effects 97/98 (1987) 1195
Chalcogenides, Transport Properties – Solids 97/98 (1987) 667
Computer Simulation, Experimental Techniques 97/98 (1987) 607
Dangling Bonds, Recombination 97/98 (1987) 639
Diodes, III–V semiconductors, Optical Properties 97/98 (1987) 1347
Diodes, Silicon, Transport Properties – Solids 97/98 (1987) 1323
Electrical Properties, Electronic Structure 97/98 (1987) 611
Electrical Properties, Thin Films, Transport Properties – Solids 97/98 (1987) 1055
Electronic Conductivity 97/98 (1987) 627
Electronic Conductivity 97/98 (1987) 911
Electronic Conductivity, Photoinduced Effects 97/98 (1987) 791
Electronic Structure 97/98 (1987) 603
Electronic Structure, Optical Properties 97/98 (1987) 699
Gap States, Stress Relaxation 97/98 (1987) 819

Glow Discharge, Silicon Alloys	97/98 (1987) 1447
Glow Discharge, Silicon Alloys, Transport Properties – Solids	97/98 (1987) 1071
Infra-red Absorption, Optical Properties	97/98 (1987) 1075
Interfaces, Thin Films	97/98 (1987) 967
Optical Properties, Silicon	97/98 (1987) 727
Relaxation	97/98 (1987) 113
Relaxation	97/98 (1987) 1035
Scanning Electron Microscopy, Transient Effects	97/98 (1987) 1327
Silicon	97/98 (1987) 575
Silicon	97/98 (1987) 731
Silicon, Solar Cells, Thin Films	97/98 (1987) 1355
Silicon, Switching	97/98 (1987) 1335
Silicon, Transient Effects	97/98 (1987) 587
Silicon Alloys, Thin Films	97/98 (1987) 1019
Stäbler–Wronski Effect	97/98 (1987) 823
Superlattices, Transport Properties – Solids	97/98 (1987) 939
Transient Effects	97/98 (1987) 599
Transport Properties – Solids	97/98 (1987) 479
Transport Properties – Solids	97/98 (1987) 739

Photoinduced Effects

Absorption, Stäbler–Wronski Effect	97/98 (1987) 787
Chalcogenides	97/98 (1987) 1223
Chalcogenides, Optical Properties	97/98 (1987) 1207
Chalcogenides, Photoconductivity	97/98 (1987) 1195
Electrical Properties, X-ray Diffraction	97/98 (1987) 679
Electronic Conductivity, Photoconductivity	97/98 (1987) 791
Gap States	97/98 (1987) 1063
Germanium, Silicon	97/98 (1987) 1067
Optical Properties	97/98 (1987) 615
Optical Properties, Silicon	97/98 (1987) 651

Polymers

Carbon, Deposition Techniques	97/98 (1987) 1451
Electronic Conductivity	97/98 (1987) 1111

Porosity

Deposition Techniques, Silicon	97/98 (1987) 1431

Pressure Effects

Germanates	97/98 (1987) 1115
Phase Transition, Structure	97/98 (1987) 391

Radiation Effects

Chalcogenides, Diffusion	97/98 (1987) 1247
Chalcogenides, Electron Spin Resonance	97/98 (1987) 1179
Chalcogenides, EXAFS	97/98 (1987) 1119
Chalcogenides, Impurities	97/98 (1987) 1243
Chalcogenides, Small Angle X-ray Scattering	97/98 (1987) 1215
Chalcogenides, Thin Films	97/98 (1987) 1239
Density of States, Electron Spin Resonance	97/98 (1987) 795

Raman Spectra

Acoustic Properties, Phonons	97/98 (1987) 859
Chalcogenides, Neutron Diffraction	97/98 (1987) 167

Electron Spin Resonance, Silicon	97/98 (1987)	91
Germanium, Silicon	97/98 (1987)	163
Kinetics, Theory	97/98 (1987)	487
Optical Properties, Structure	97/98 (1987)	387
Silicon, Structure	97/98 (1987)	399
Silicon Alloys, Structure, Superlattices	97/98 (1987)	887
Structure	97/98 (1987)	39
Structure, X-ray Diffraction	97/98 (1987)	203
Recombination		
Dangling Bonds, Photoconductivity	97/98 (1987)	639
Interfaces, Optical Properties	97/98 (1987)	931
Luminescence, Optical Properties	97/98 (1987)	915
Silicon	97/98 (1987)	579
Relaxation		
Electrical Properties, Photo-emission	97/98 (1987)	595
Infra-red Absorption, Optical Properties	97/98 (1987)	109
Optical Properties	97/98 (1987)	141
Photoconductivity	97/98 (1987)	113
Photoconductivity	97/98 (1987)	1035
Silicon, Time-Resolved Spectroscopy	97/98 (1987)	591
Structure, X-ray Diffraction	97/98 (1987)	171
Transport Properties – Solids	97/98 (1987)	619
Scanning Electron Microscopy		
Photoconductivity, Transient Effects	97/98 (1987)	1327
Secondary Ion Mass Spectroscopy		
Auger Electron Spectroscopy, Silicon Alloys	97/98 (1987)	951
Semiconductors		
Amorphous Solids, Electronic Structure	97/98 (1987)	95
Defects, Electronic Structure	97/98 (1987)	415
Thin Films, Transport Properties – Solids	97/98 (1987)	963
Time-Resolved Spectroscopy	97/98 (1987)	145
Short-Range Order		
Medium-Range Order, Structure	97/98 (1987)	159
Silica		
Computer Simulation, Surface Properties	97/98 (1987)	195
Infra-red Absorption	97/98 (1987)	1051
Silicates		
Hopping, Transport Properties – Solids	97/98 (1987)	523
Silicon		
Applications, Thin Films	97/98 (1987)	297
Applications, Transistors	97/98 (1987)	301
Applications, Transistors	97/98 (1987)	313
Applications, Transistors	97/98 (1987)	1291
Bonding	97/98 (1987)	1043
Capacitance Methods, Electrical Properties, Stability	97/98 (1987)	803

Chalcogenides, Optical Properties	97/98 (1987)	1199
Computer Simulation, Electrical Properties, Heterojunctions	97/98 (1987)	983
Computer Simulation, Structure	97/98 (1987)	175
Dangling Bonds, Density of States	97/98 (1987)	715
Defects	97/98 (1987)	463
Density of States, Deposition Techniques	97/98 (1987)	1391
Density of States, Electronic Structure	97/98 (1987)	747
Density of States, Silicon Alloys	97/98 (1987)	1059
Density of States, Stäbler–Wronski Effect	97/98 (1987)	811
Density of States, Theory	97/98 (1987)	499
Density of States, Transport Properties – Solids	97/98 (1987)	563
Deposition Techniques, Electronic Structure	97/98 (1987)	1435
Deposition Techniques, Porosity	97/98 (1987)	1431
Deposition Techniques, Thin Films	97/98 (1987)	265
Dielectric Properties, Liquid Semiconductors	97/98 (1987)	1267
Diffusion, Impurities	97/98 (1987)	353
Diodes, Photoconductivity, Transport Properties – Solids	97/98 (1987)	1323
Electrical Properties	97/98 (1987)	695
Electrical Properties, Optical Properties	97/98 (1987)	1375
Electrical Properties, Time-Resolved Spectroscopy	97/98 (1987)	121
Electron Spin Resonance, Raman Spectra	97/98 (1987)	91
Electronic Structure	97/98 (1987)	583
Electronic Structure, Impurities	97/98 (1987)	495
Electronic Structure, Theory	97/98 (1987)	459
Electronic Structure, Transport Properties – Solids	97/98 (1987)	15
Fabrication, Thin Films	97/98 (1987)	281
Germanium, Photoinduced Effects	97/98 (1987)	1067
Germanium, Raman Spectra	97/98 (1987)	163
Glow Discharge	97/98 (1987)	623
Growth Kinetics, Transport Properties – Solids	97/98 (1987)	1399
Heterojunctions, Photo Voltage	97/98 (1987)	1363
Hydrogen Effects, Structure	97/98 (1987)	1395
Image Sensors, Transistors	97/98 (1987)	1343
Impurities, Nuclear Magnetic Resonance	97/98 (1987)	357
Infra-red Absorption, Lattice Dynamics	97/98 (1987)	839
Infra-red Absorption, Structure	97/98 (1987)	1387
Injection of Carriers, Luminescence	97/98 (1987)	1311
Interfaces, Photo-emission	97/98 (1987)	851
Kinetics	97/98 (1987)	783
Magnetic Properties	97/98 (1987)	631
Memory Behaviour, Switching	97/98 (1987)	1331
Mössbauer Effect, Structure	97/98 (1987)	361
MultiLayers, Silicon Nitride, Superlattices	97/98 (1987)	23
Neutron Diffraction, Structure	97/98 (1987)	337
Optical Properties, Photoconductivity	97/98 (1987)	727
Optical Properties, Photoinduced Effects	97/98 (1987)	651
Optical Properties, X-ray Diffraction	97/98 (1987)	191
Photo-emission	97/98 (1987)	647
Photo-emission	97/98 (1987)	707
Photo-emission, Surface Properties	97/98 (1987)	87
Photo-emission, Surface Properties	97/98 (1987)	847
Photo Voltage, Surface Properties	97/98 (1987)	567
Photoconductivity	97/98 (1987)	575
Photoconductivity	97/98 (1987)	731

Photoconductivity, Solar Cells, Thin Films 97/98 (1987) 1355
Photoconductivity, Switching 97/98 (1987) 1335
Photoconductivity, Transient Effects 97/98 (1987) 587
Raman Spectra, Structure 97/98 (1987) 399
Recombination 97/98 (1987) 579
Relaxation, Time-Resolved Spectroscopy 97/98 (1987) 591
Solar Cells, Superlattices 97/98 (1987) 289
Structure 97/98 (1987) 1039
Structure, Theory 97/98 (1987) 503
Tails, Time-Resolved Spectroscopy 97/98 (1987) 117
Thermal Conductivity 97/98 (1987) 711
Time-Resolved Spectroscopy 97/98 (1987) 125
Transport Properties – Solids 97/98 (1987) 571

Silicon Alloys
Auger Electron Spectroscopy, Secondary Ion Mass Spectroscopy 97/98 (1987) 951
Defects, Electron Spin Resonance 97/98 (1987) 1015
Density of States 97/98 (1987) 1455
Density of States, Electronic Structure 97/98 (1987) 507
Density of States, Optical Properties, Theory 97/98 (1987) 515
Density of States, Silicon 97/98 (1987) 1059
Density of States, Thermoelectric Power 97/98 (1987) 511
Electrical Properties 97/98 (1987) 419
Electrical Properties, Structure 97/98 (1987) 1027
Electron Spin Resonance, Gap States 97/98 (1987) 1011
Electronic Conductivity, Sputtering 97/98 (1987) 955
Electronic Structure, Photo-emission 97/98 (1987) 407
Electronic Structure, Transient Effects 97/98 (1987) 1023
Electronic Structure, X-ray Emission 97/98 (1987) 843
EXAFS 97/98 (1987) 365
Glow Discharge, Photoconductivity 97/98 (1987) 1447
Glow Discharge, Photoconductivity, Transport Properties – Solids 97/98 (1987) 1071
Heterojunctions, Structure 97/98 (1987) 895
Heterojunctions, Transport Properties – Solids 97/98 (1987) 1319
Injection of Carriers, Optical Properties 97/98 (1987) 293
Luminescence, Superlattices 97/98 (1987) 883
Optical Properties 97/98 (1987) 991
Optical Properties, Photo-emission 97/98 (1987) 451
Optical Properties, Structure 97/98 (1987) 1087
Optical Properties, Thin Films 97/98 (1987) 999
Optical Properties, X-ray Emission 97/98 (1987) 1091
Photoconductivity, Thin Films 97/98 (1987) 1019
Raman Spectra, Structure, Superlattices 97/98 (1987) 887
Solar Cells 97/98 (1987) 1303

Silicon Nitride
Dangling Bonds, Stability, Transistors 97/98 (1987) 321
Density of States, X-ray Emission 97/98 (1987) 827
Electrical Properties 97/98 (1987) 1003
Interfaces, Trapping 97/98 (1987) 891
Multilayers, Silicon, Superlattices 97/98 (1987) 23

Sintering
Dangling Bonds, Electron Microscopy, Gap States 97/98 (1987) 79

Small Angle X-ray Scattering
Chalcogenides, Radiation Effects 97/98 (1987) 1215

Solar Cells
Computer Simulation 97/98 (1987) 1307
Photoconductivity, Silicon, Thin Films 97/98 (1987) 1355
Silicon, Superlattices 97/98 (1987) 289
Silicon Alloys 97/98 (1987) 1303
Transport Properties – Solids 97/98 (1987) 309

Sputtering
Crystallization, Thermodynamics 97/98 (1987) 947
Dangling Bonds, Electron Spin Resonance, Glow Discharge 97/98 (1987) 67
Electron Spin Resonance, Electronic Structure, Infra-red Absorption, Optical Properties 97/98 (1987) 831
Electronic Conductivity, Silicon Alloys 97/98 (1987) 955

Stability
Capacitance Methods, Electrical Properties, Silicon 97/98 (1987) 803
Dangling Bonds, Silicon Nitride, Transistors 97/98 (1987) 321

Stäbler–Wronski Effect
Absorption, Photoinduced Effects 97/98 (1987) 787
Density of States, Silicon 97/98 (1987) 811
Photoconductivity 97/98 (1987) 823

Stress Relaxation
Gap States, Photoconductivity 97/98 (1987) 819

Structure
Bonding, Medium-Range Order 97/98 (1987) 155
Carbon, Electronic Structure 97/98 (1987) 199
Chalcogenides 97/98 (1987) 379
Chalcogenides 97/98 (1987) 439
Chalcogenides 97/98 (1987) 447
Chalcogenides 97/98 (1987) 1275
Chalcogenides, Computer Simulation 97/98 (1987) 383
Chalcogenides, Liquids 97/98 (1987) 1251
Chalcogenides, Liquids 97/98 (1987) 1271
Computer Simulation, Liquids 97/98 (1987) 187
Computer Simulation, Silicon 97/98 (1987) 175
Crystallization, Liquids 97/98 (1987) 1259
Crystallization, Phase Separation 97/98 (1987) 55
Electrical Properties, Silicon Alloys 97/98 (1987) 1027
Electron Spin Resonance 97/98 (1987) 691
Electronic Structure, Thin Films 97/98 (1987) 179
EXAFS 97/98 (1987) 403
EXAFS, Tetrahedral Materials 97/98 (1987) 435
Glow Discharge, Multilayers 97/98 (1987) 1439
Heterojunctions, Silicon Alloys 97/98 (1987) 895
Hydrogen Effects, Silicon 97/98 (1987) 1395
Infra-red Absorption, Silicon 97/98 (1987) 1387
Liquid Semiconductors, Neutron Diffraction 97/98 (1987) 1263
Liquid Semiconductors, Neutron Diffraction 97/98 (1987) 1283

Medium-Range Order, Short-Range Order 97/98 (1987) 159
Mössbauer Effect, Silicon 97/98 (1987) 361
Neutron Diffraction 97/98 (1987) 329
Neutron Diffraction, Silicon 97/98 (1987) 337
Nuclear Magnetic Resonance 97/98 (1987) 345
Optical Properties, Raman Spectra 97/98 (1987) 387
Optical Properties, Silicon Alloys 97/98 (1987) 1087
Oxides, Phase Separation 97/98 (1987) 423
Phase Transition, Pressure Effects 97/98 (1987) 391
Photo-emission 97/98 (1987) 1211
Raman Spectra 97/98 (1987) 39
Raman Spectra, Silicon 97/98 (1987) 399
Raman Spectra, Silicon Alloys, Superlattices 97/98 (1987) 887
Raman Spectra, X-ray Diffraction 97/98 (1987) 203
Relaxation, X-ray Diffraction 97/98 (1987) 171
Silicon 97/98 (1987) 1039
Silicon, Theory 97/98 (1987) 503
X-ray Diffraction 97/98 (1987) 183

Superlattices
Absorption, Optical Properties 97/98 (1987) 927
Applications, Transport Properties – Solids 97/98 (1987) 317
Defects, Electrical Properties, Electron Spin Resonance 97/98 (1987) 875
Density of States, Optical Properties 97/98 (1987) 751
Electron Diffraction 97/98 (1987) 341
Electron Spin Resonance, Luminescence 97/98 (1987) 867
Infra-red Absorption, Optical Properties 97/98 (1987) 943
Luminescence, Optical Properties 97/98 (1987) 919
Luminescence, Silicon Alloys 97/98 (1987) 883
Multilayers, Silicon, Silicon Nitride 97/98 (1987) 23
Photo-emission, Transport Properties – Solids 97/98 (1987) 907
Photoconductivity, Transport Properties – Solids 97/98 (1987) 939
Raman Spectra, Silicon Alloys, Structure 97/98 (1987) 887
Silicon, Solar Cells 97/98 (1987) 289
Transport Properties – Liquids 97/98 (1987) 871

Surface Properties
Applications, Crystallization 97/98 (1987) 1315
Applications, Transport Properties – Solids 97/98 (1987) 1359
Chalcogenides, Ion Implantation 97/98 (1987) 443
Computer Simulation, Silica 97/98 (1987) 195
Deposition Techniques 97/98 (1987) 261
Electronic Structure, Photo-emission 97/98 (1987) 1411
Hydrogenation, Photo-emission 97/98 (1987) 1407
Photo-emission 97/98 (1987) 703
Photo-emission, Silicon 97/98 (1987) 87
Photo-emission, Silicon 97/98 (1987) 847
Photo Voltage, Silicon 97/98 (1987) 567

Switching
Memory Behaviour, Silicon 97/98 (1987) 1331
Photoconductivity, Silicon 97/98 (1987) 1335

Tails
Density of States 97/98 (1987) 101
Silicon, Time-Resolved Spectroscopy 97/98 (1987) 117

Tetrahedral Materials
Computer Simulation 97/98 (1987) 349
EXAFS, Structure 97/98 (1987) 435

Theory
Absorption, Optical Properties 97/98 (1987) 527
Defects, Thermodynamics 97/98 (1987) 467
Density of States, Optical Properties, Silicon Alloys 97/98 (1987) 515
Density of States, Silicon 97/98 (1987) 499
Diffusion 97/98 (1987) 245
Electronic Conductivity, Transport Properties – Solids 97/98 (1987) 229
Electronic Conductivity, Transport Properties – Solids 97/98 (1987) 475
Electronic Structure, Impurities 97/98 (1987) 491
Electronic Structure, Impurity Conduction 97/98 (1987) 237
Electronic Structure, Silicon 97/98 (1987) 459
High Field Effects, Hopping 97/98 (1987) 547
Kinetics, Raman Spectra 97/98 (1987) 487
Localization, Mobility Edge 97/98 (1987) 531
Metal–Insulator Transition 97/98 (1987) 217
Silicon, Structure 97/98 (1987) 503
Time-Resolved Spectroscopy, Transient Effects 97/98 (1987) 455

Thermal Conductivity
Silicon 97/98 (1987) 711

Thermodynamics
Crystallization, Sputtering 97/98 (1987) 947
Defects, Theory 97/98 (1987) 467

Thermoelectric Power
Chalcogenides, Electronic Conductivity 97/98 (1987) 1139
Density of States, Silicon Alloys 97/98 (1987) 511
Electronic Conductivity 97/98 (1987) 539

Thin Films
Applications, Silicon 97/98 (1987) 297
Chalcogenides, Optical Properties 97/98 (1987) 1219
Chalcogenides, Radiation Effects 97/98 (1987) 1239
Deposition Techniques, Silicon 97/98 (1987) 265
Electrical Properties, Photoconductivity, Transport Properties – Solids 97/98 (1987) 1055
Electron Spin Resonance, Electronic Structure 97/98 (1987) 1083
Electronic Conductivity, Transport Properties – Solids 97/98 (1987) 671
Electronic Structure, Structure 97/98 (1987) 179
Ellipsometry, Growth Kinetics 97/98 (1987) 1403
Fabrication, Microwave 97/98 (1987) 277
Fabrication, Silicon 97/98 (1987) 281
Germanium, Optical Properties 97/98 (1987) 1155
Impurities 97/98 (1987) 1419
Interfaces, Photoconductivity 97/98 (1987) 967
Ion Implantation, Phosphates 97/98 (1987) 273

Kinetics 97/98 (1987) 1367
Kinetics, Lasers 97/98 (1987) 1443
Optical Properties, Silicon Alloys 97/98 (1987) 999
Photoconductivity, Silicon, Solar Cells 97/98 (1987) 1355
Photoconductivity, Silicon Alloys 97/98 (1987) 1019
Semiconductors, Transport Properties – Solids 97/98 (1987) 963

Time-Resolved Spectroscopy
Electrical Properties, Silicon 97/98 (1987) 121
Relaxation, Silicon 97/98 (1987) 591
Semiconductors 97/98 (1987) 145
Silicon 97/98 (1987) 125
Tails, Silicon 97/98 (1987) 117
Theory, Transient Effects 97/98 (1987) 455

Transient Effects
Electronic Conductivity 97/98 (1987) 129
Electronic Structure, Silicon Alloys 97/98 (1987) 1023
Photoconductivity 97/98 (1987) 599
Photoconductivity, Scanning Electron Microscopy 97/98 (1987) 1327
Photoconductivity, Silicon 97/98 (1987) 587
Theory, Time-Resolved Spectroscopy 97/98 (1987) 455

Transistors
Applications, Silicon 97/98 (1987) 301
Applications, Silicon 97/98 (1987) 313
Applications, Silicon 97/98 (1987) 1291
Dangling Bonds, Electronic Structure 97/98 (1987) 1339
Dangling Bonds, Silicon Nitride, Stability 97/98 (1987) 321
Experimental Techniques, Glow Discharge 97/98 (1987) 735
Image Sensors, Silicon 97/98 (1987) 1343
Trapping 97/98 (1987) 903

Transport Properties – Liquids
Chalcogenides, Transport Properties – Solids 97/98 (1987) 1231
Superlattices 97/98 (1987) 871

Transport Properties – Solids
Applications 97/98 (1987) 305
Applications, Computer Simulation, Electronic Conductivity 97/98 (1987) 1299
Applications, Superlattices 97/98 (1987) 317
Applications, Surface Properties 97/98 (1987) 1359
Capacitance Methods, Electrical Properties 97/98 (1987) 723
Chalcogenides, Photoconductivity 97/98 (1987) 667
Chalcogenides, Transport Properties – Liquids 97/98 (1987) 1231
Computer Simulation, Phase Transition 97/98 (1987) 221
Dangling Bonds, Electronic Conductivity 97/98 (1987) 799
Density of States, Silicon 97/98 (1987) 563
Diffusion, Electronic Conductivity, Phase Transition 97/98 (1987) 759
Diodes, Photoconductivity, Silicon 97/98 (1987) 1323
Electrical Properties 97/98 (1987) 635
Electrical Properties, Photoconductivity, Thin Films 97/98 (1987) 1055
Electronic Conductivity, Theory 97/98 (1987) 229
Electronic Conductivity, Theory 97/98 (1987) 475

Electronic Conductivity, Thin Films 97/98 (1987) 671
Electronic Structure 97/98 (1987) 655
Electronic Structure, Silicon 97/98 (1987) 15
Glow Discharge, Photoconductivity, Silicon Alloys 97/98 (1987) 1071
Growth Kinetics, Silicon 97/98 (1987) 1399
Heterojunctions, Silicon Alloys 97/98 (1987) 1319
High Field Effects 97/98 (1987) 559
Hopping, Silicates 97/98 (1987) 523
Optical Properties 97/98 (1987) 1079
Photo-emission 97/98 (1987) 855
Photo-emission, Superlattices 97/98 (1987) 907
Photoconductivity 97/98 (1987) 479
Photoconductivity 97/98 (1987) 739
Photoconductivity, Superlattices 97/98 (1987) 939
Relaxation 97/98 (1987) 619
Semiconductors, Thin Films 97/98 (1987) 963
Silicon 97/98 (1987) 571
Solar Cells 97/98 (1987) 309

Trapping
Chalcogenides, Defects 97/98 (1987) 1171
Interfaces, Silicon Nitride 97/98 (1987) 891
Transistors 97/98 (1987) 903

X-ray Diffraction
Chalcogenides, EXAFS 97/98 (1987) 411
Electrical Properties, Photoinduced Effects 97/98 (1987) 679
Optical Properties, Silicon 97/98 (1987) 191
Raman Spectra, Structure 97/98 (1987) 203
Relaxation, Structure 97/98 (1987) 171
Structure 97/98 (1987) 183

X-ray Emission
Density of States, Silicon Nitride 97/98 (1987) 827
Electronic Structure, Silicon Alloys 97/98 (1987) 843
Optical Properties, Silicon Alloys 97/98 (1987) 1091

XPS
Defects, Optical Properties 97/98 (1987) 1107
Dielectric Properties, Electronic Structure 97/98 (1987) 431